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Oh et al.

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(54) **NONVOLATILE MEMORY DEVICE AND BAD AREA MANAGING METHOD THEREOF**

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G06F 11/00 (2006.01)
G11C 11/34 (2006.01)
G11C 8/00 (2006.01)
G06F 11/10 (2006.01)
G11C 5/02 (2006.01)

(Continued)

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CPC **G06F 11/1068** (2013.01); **G06F 11/1016** (2013.01); **G06F 11/1044** (2013.01); **G06F 11/1048** (2013.01); **G06F 11/1072** (2013.01); **G11C 5/02** (2013.01); **G11C 5/025** (2013.01); **G11C 29/70** (2013.01); **G11C 29/82** (2013.01); **G11C 29/883** (2013.01); **H01L 27/0688** (2013.01); **H01L 27/11514** (2013.01); **H01L 27/11521** (2013.01); **H01L 27/11578** (2013.01); **H01L 27/281** (2013.01)

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CPC G11C 29/883; G11C 29/70; G11C 5/025; G11C 5/02; G06F 11/1068; G06F 11/1072; G06F 11/1044; G06F 11/1016; G06F 11/1048; H01L 27/0688; H01L 27/11514; H01L 27/11521; H01L 27/11578; H01L 27/281
USPC 714/718, 723, 746, 763, 768, 769, 773, 714/799, 6.1, 48; 365/185.09, 200, 201, 365/230.03, 236; 711/101, 104, 105, 152, 711/170, 202

See application file for complete search history.

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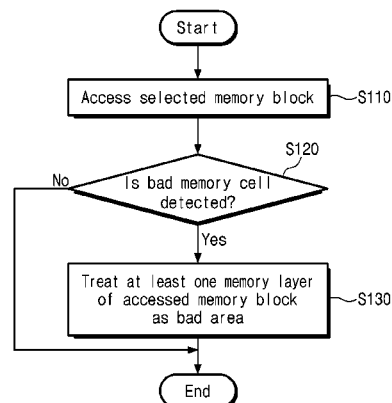
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(57) **ABSTRACT**

Example embodiments relate to a bad area managing method of a nonvolatile memory device. The nonvolatile memory device may include a plurality of memory blocks and each block may contain memory layers stacked on a substrate. According to example embodiments, a method includes accessing one of the memory blocks, judging whether the accessed memory block includes at least one memory layer containing a bad memory cell. If a bad memory cell is detected, the method may further include configuring the memory device to treat the at least one memory layer of the accessed memory block as a bad area.

20 Claims, 25 Drawing Sheets



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Fig. 1

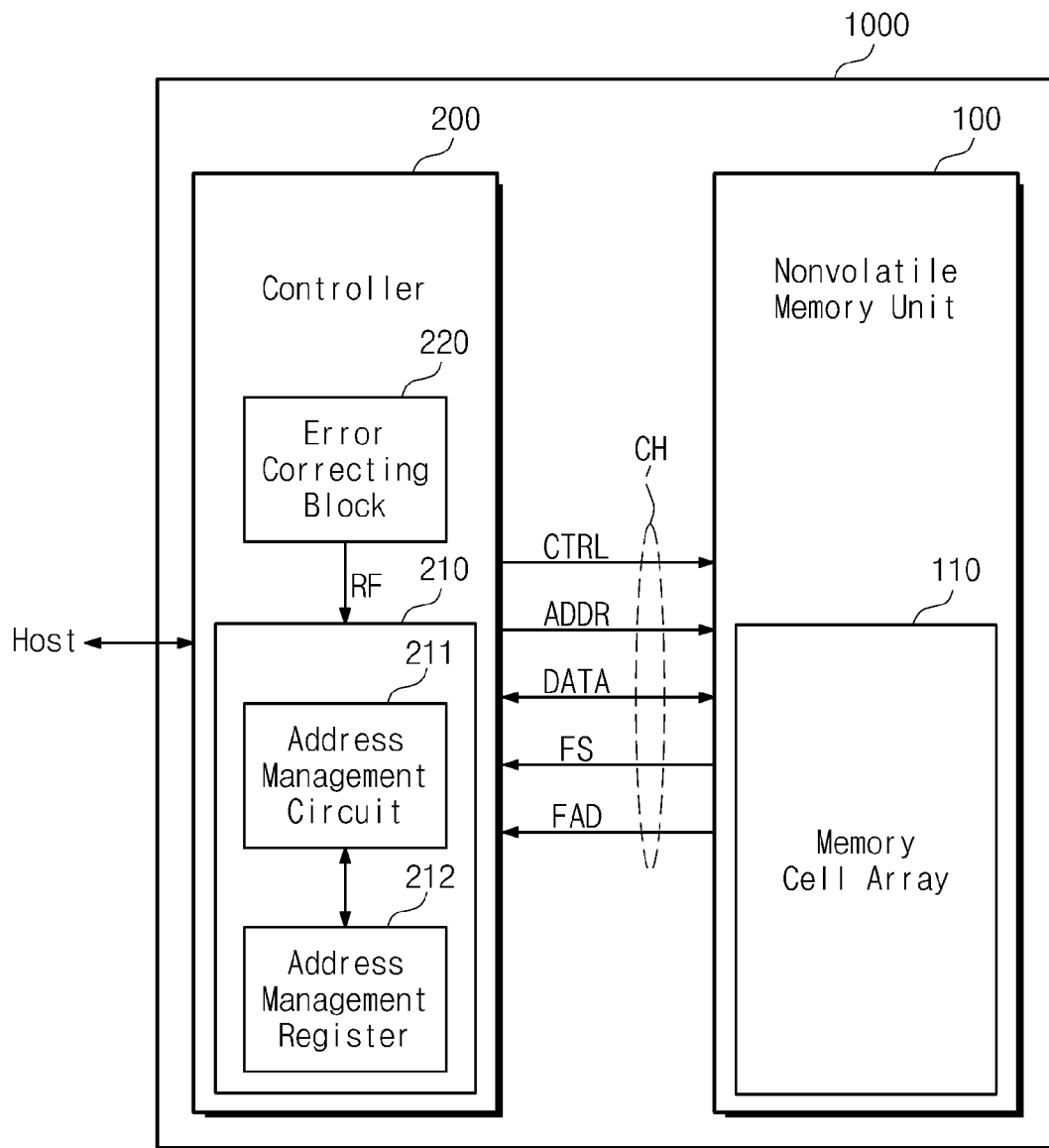


Fig. 2

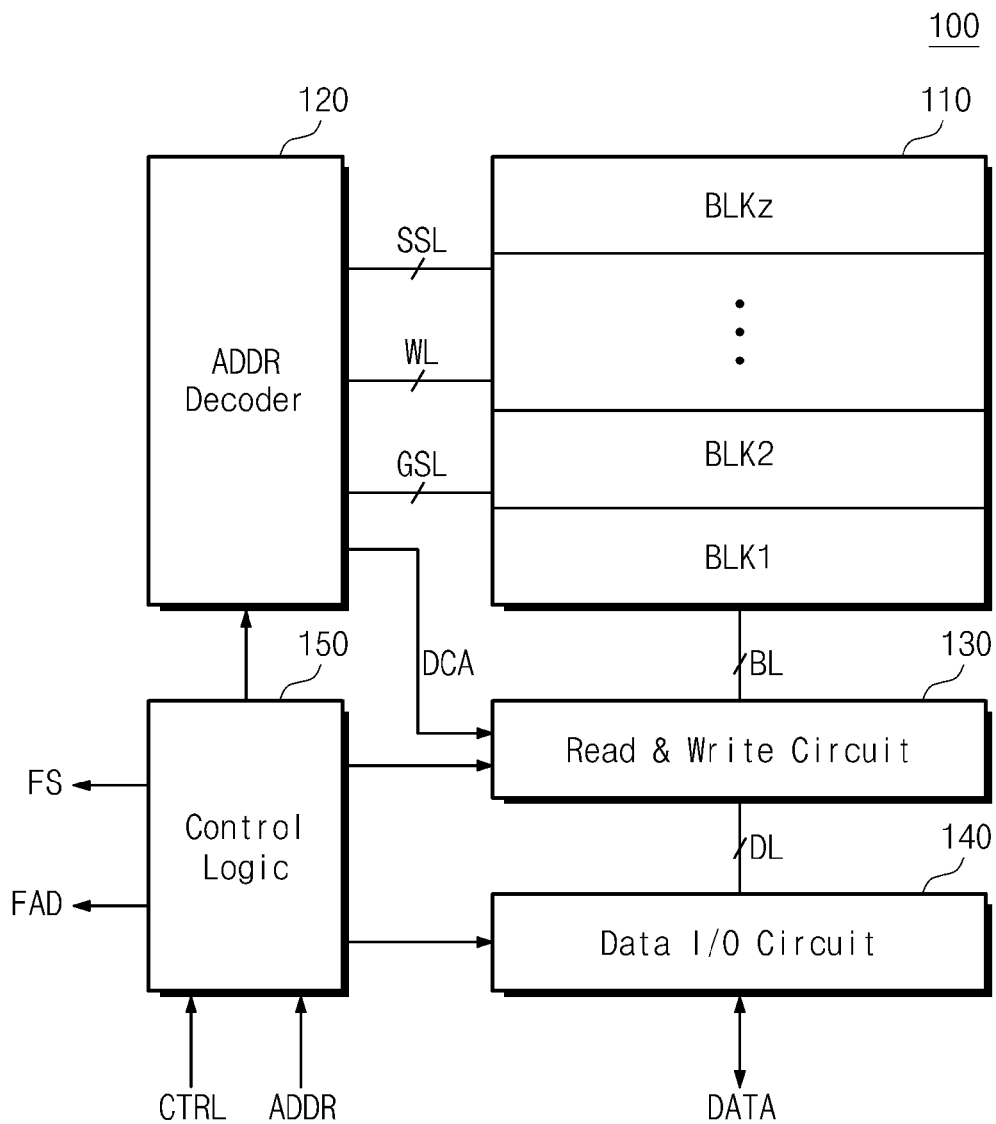


Fig. 3

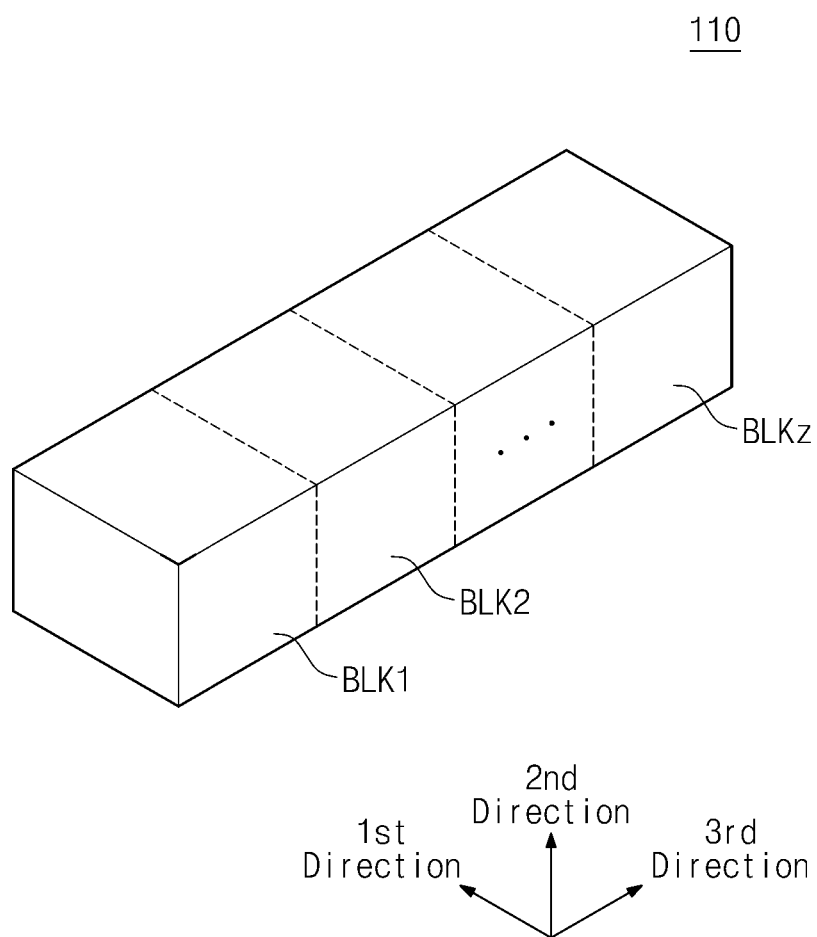


Fig. 6

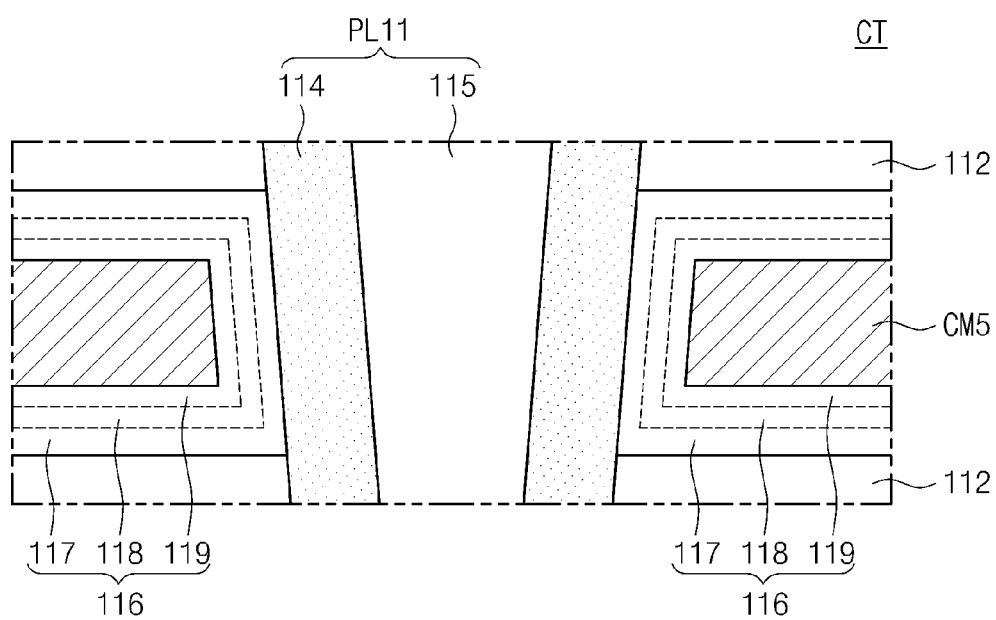


Fig. 7

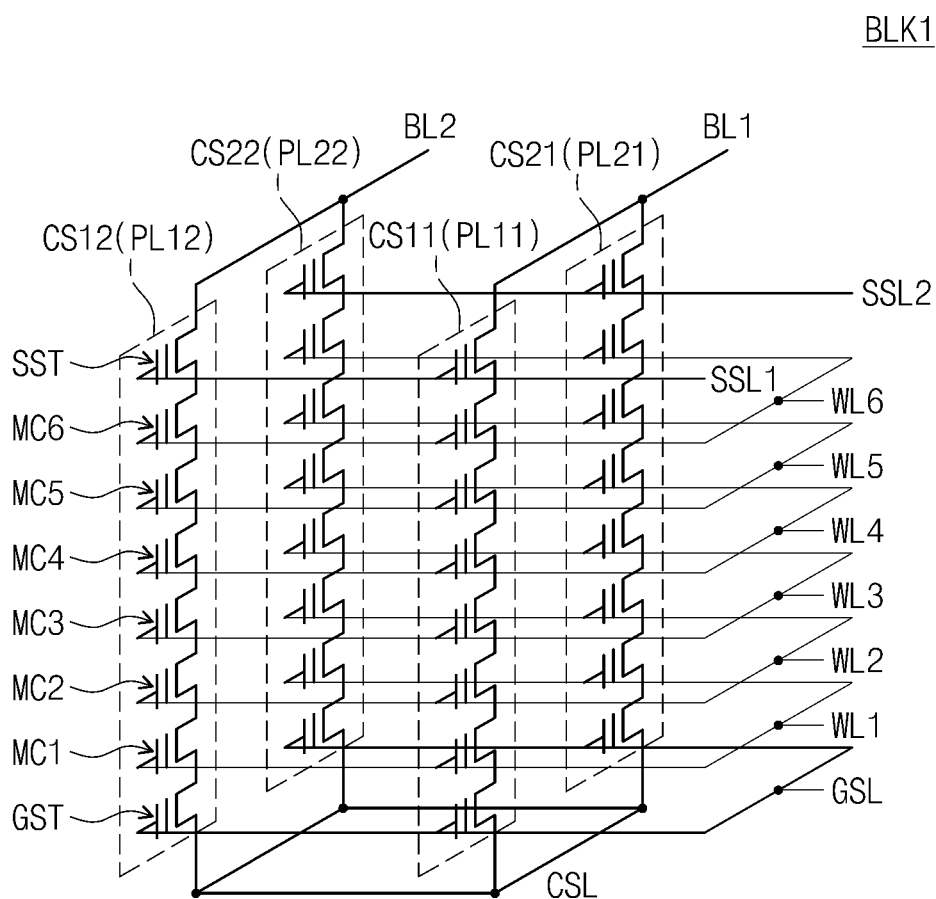


Fig. 8

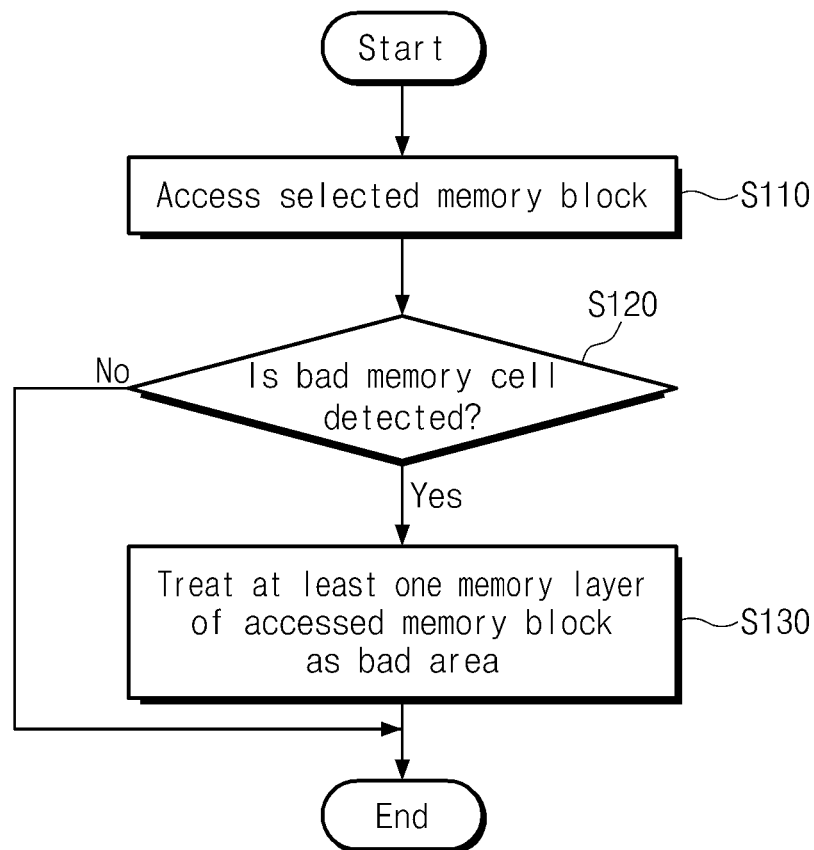


Fig. 9

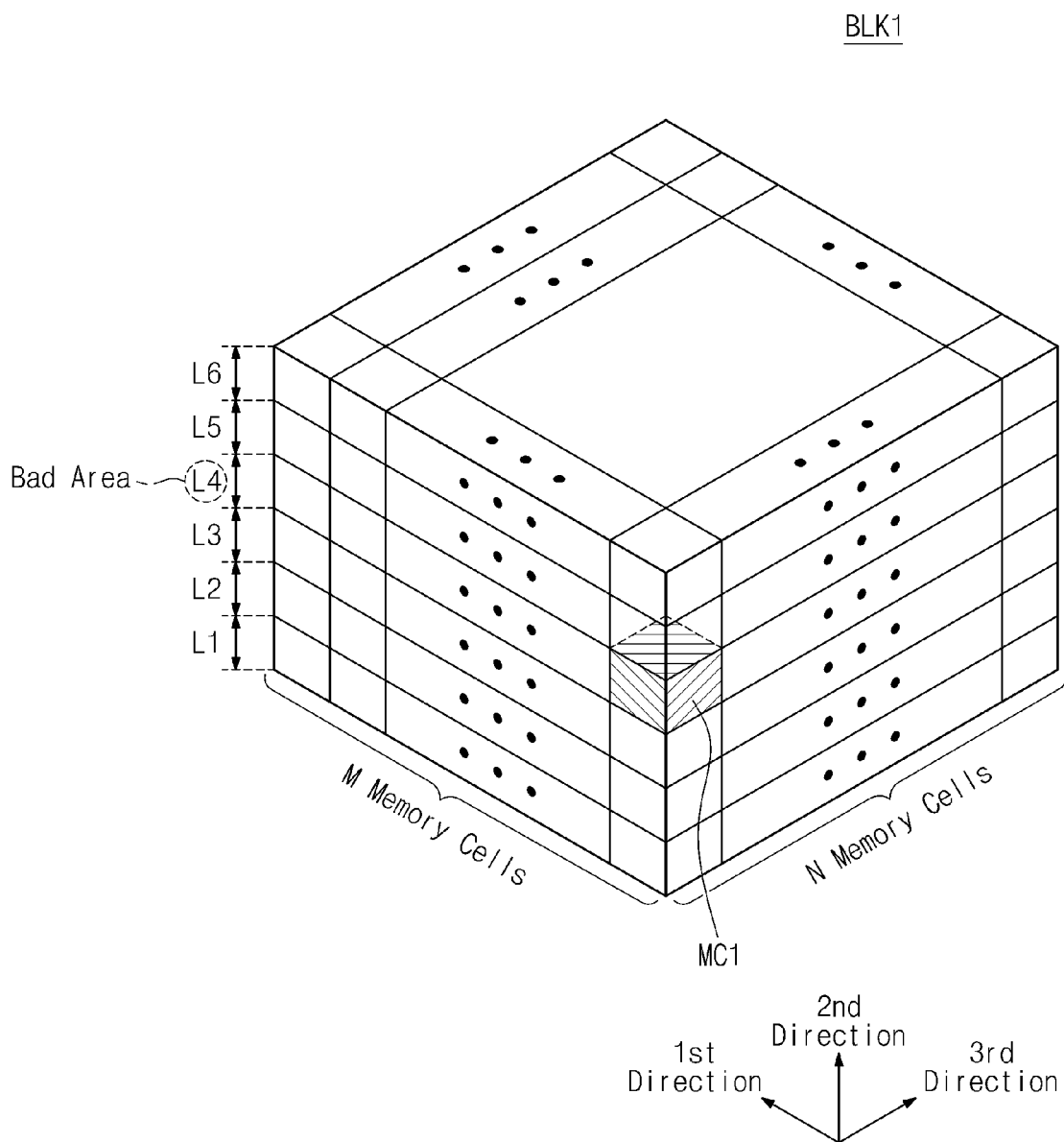


Fig. 10

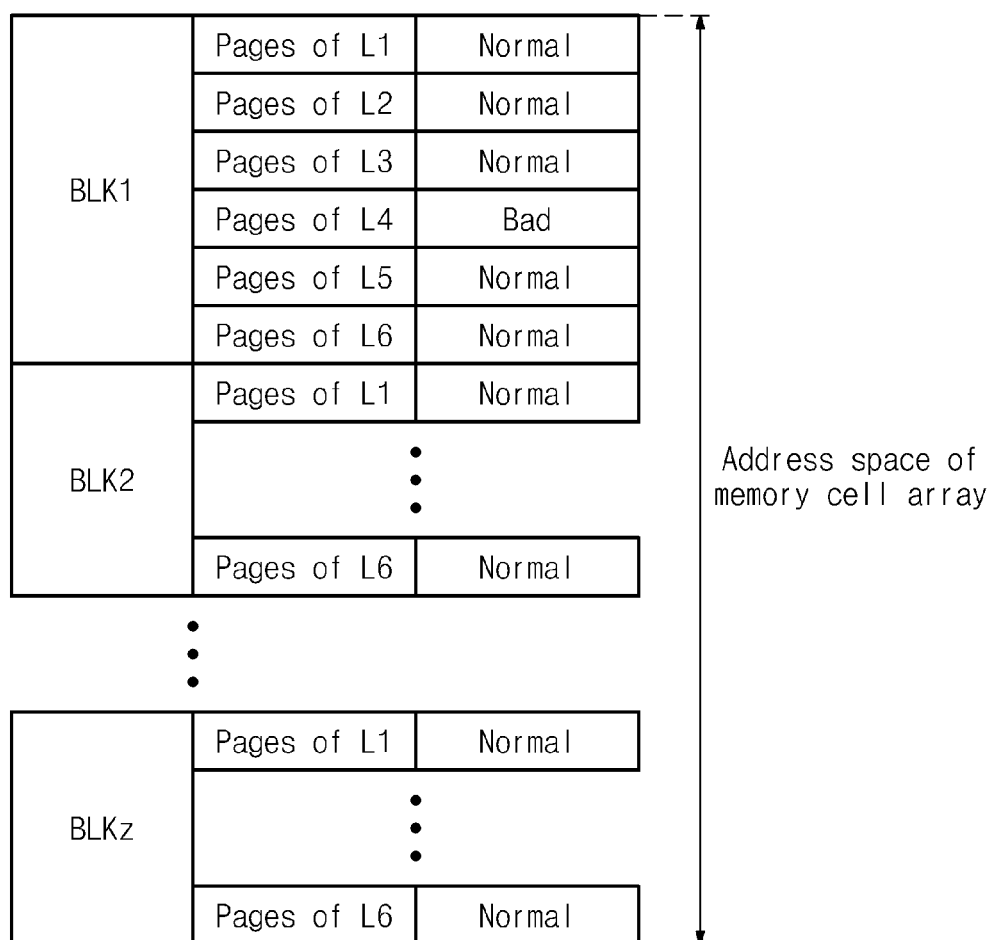


Fig. 11

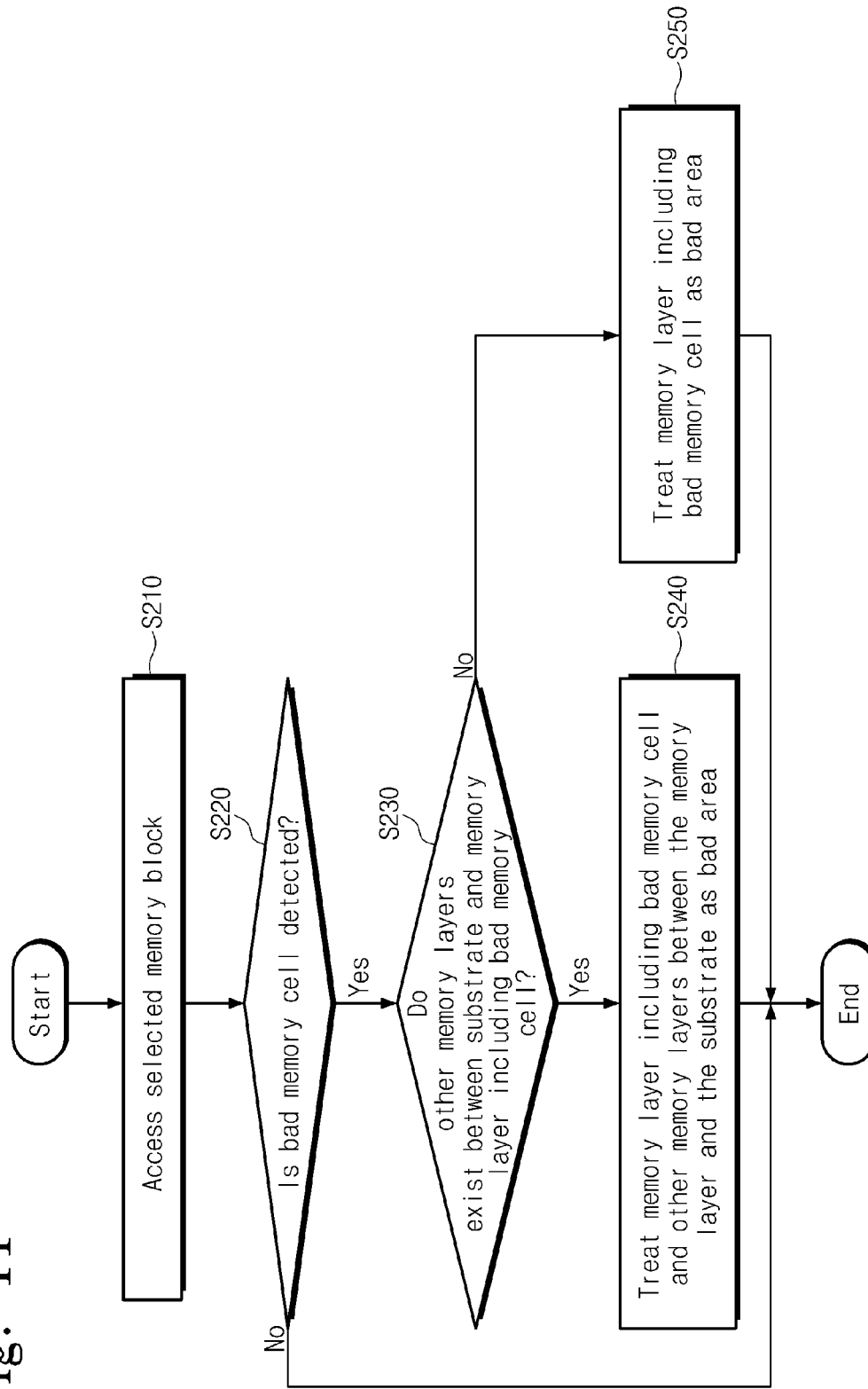


Fig. 12

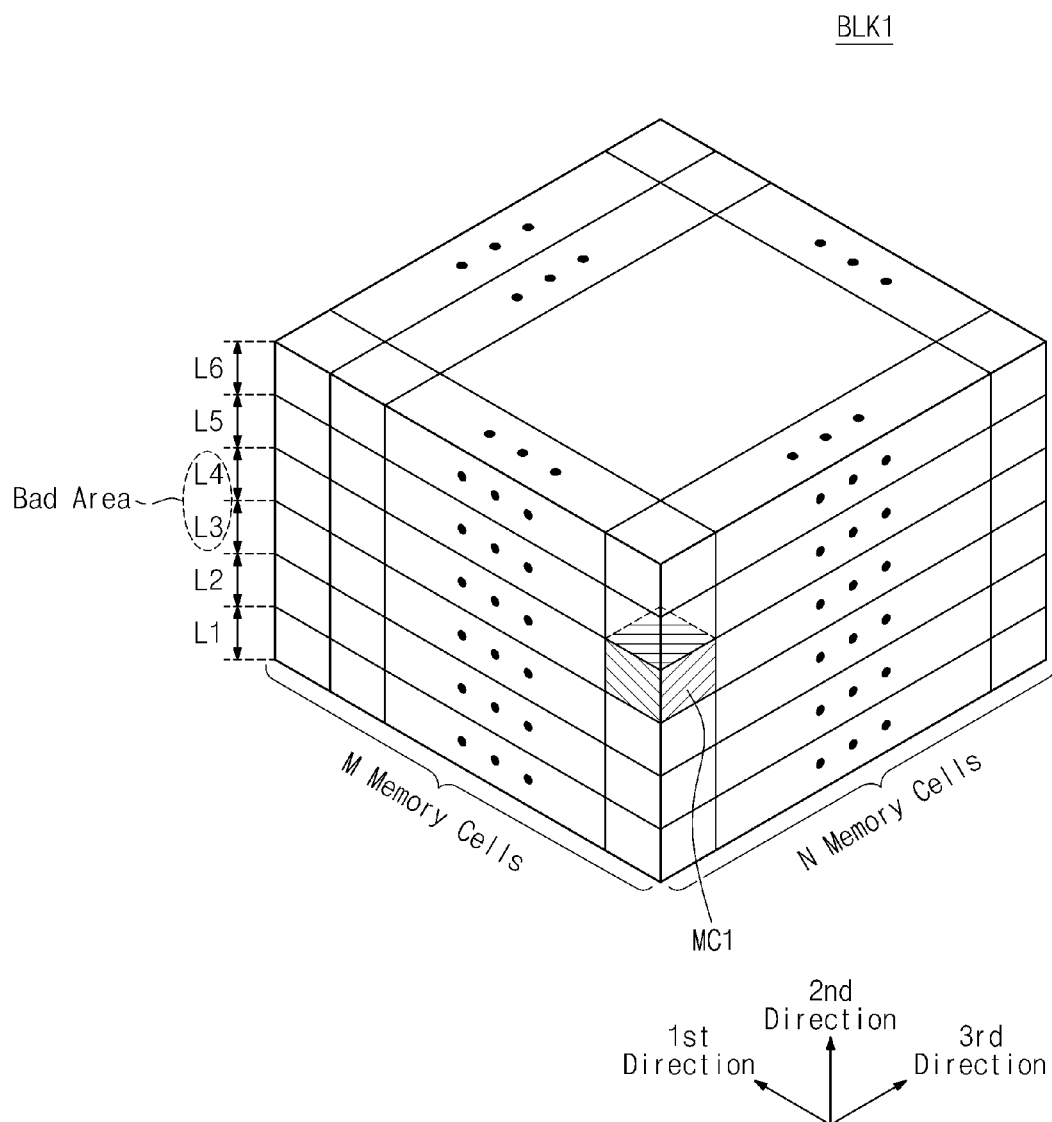
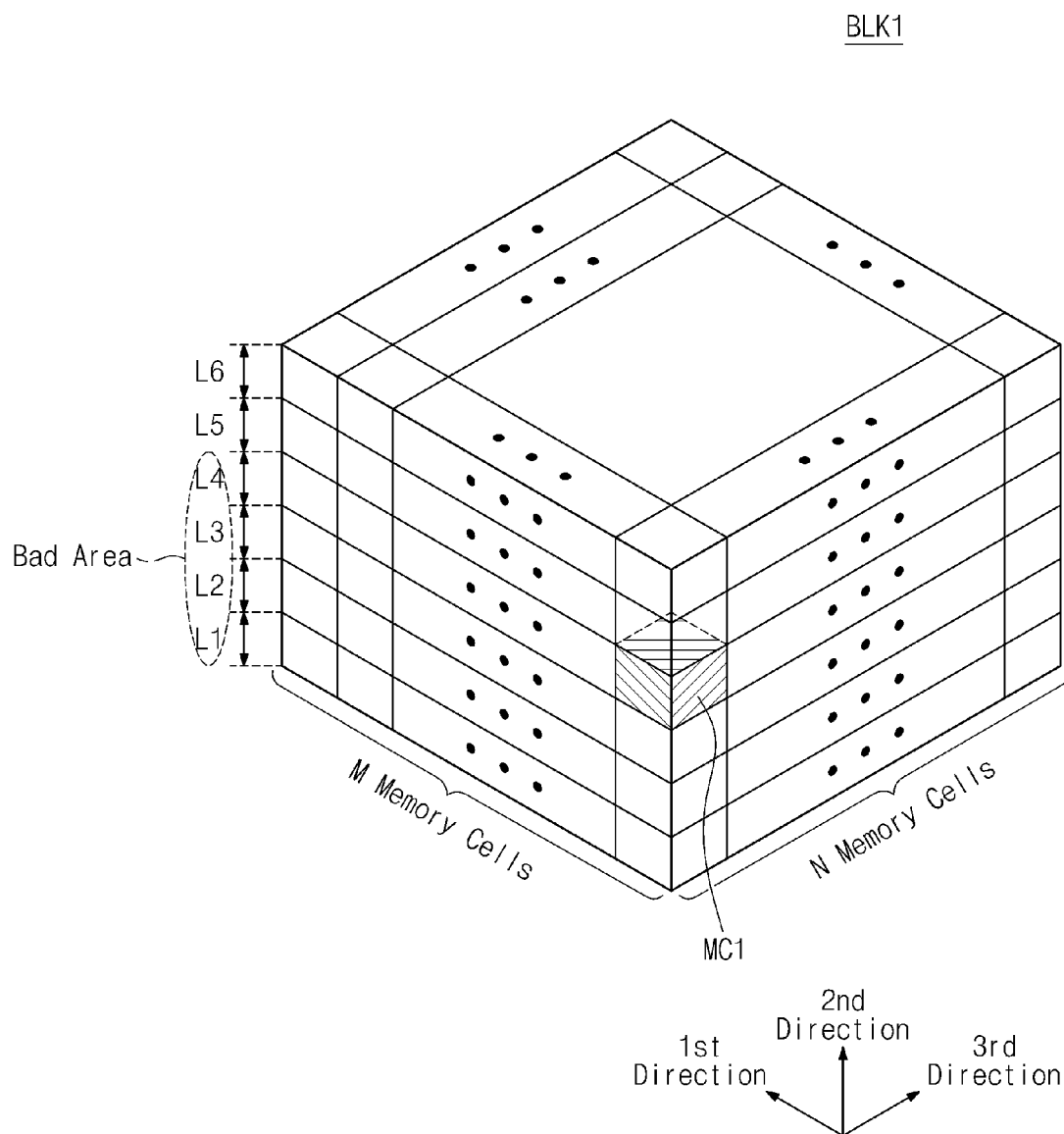
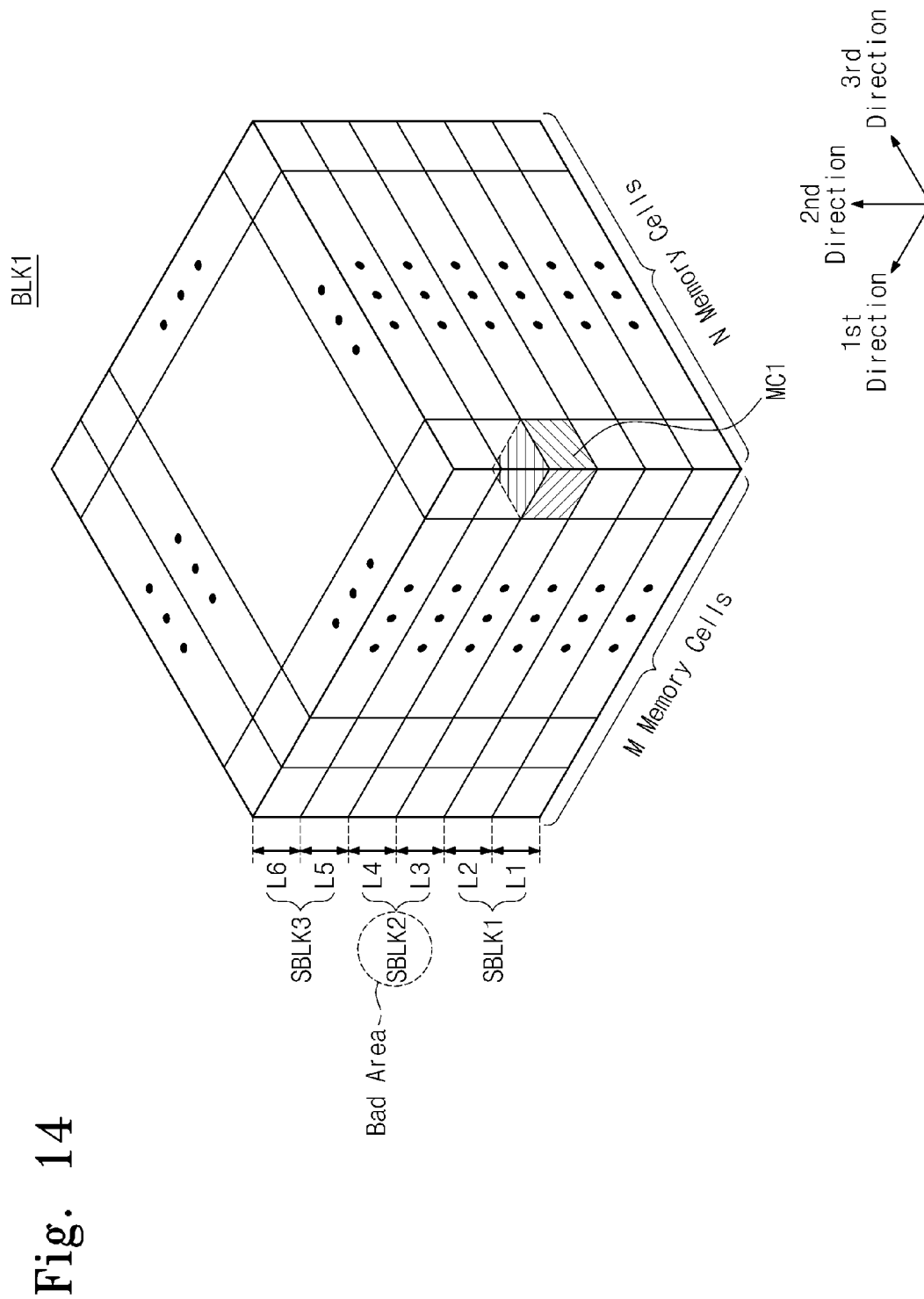


Fig. 13





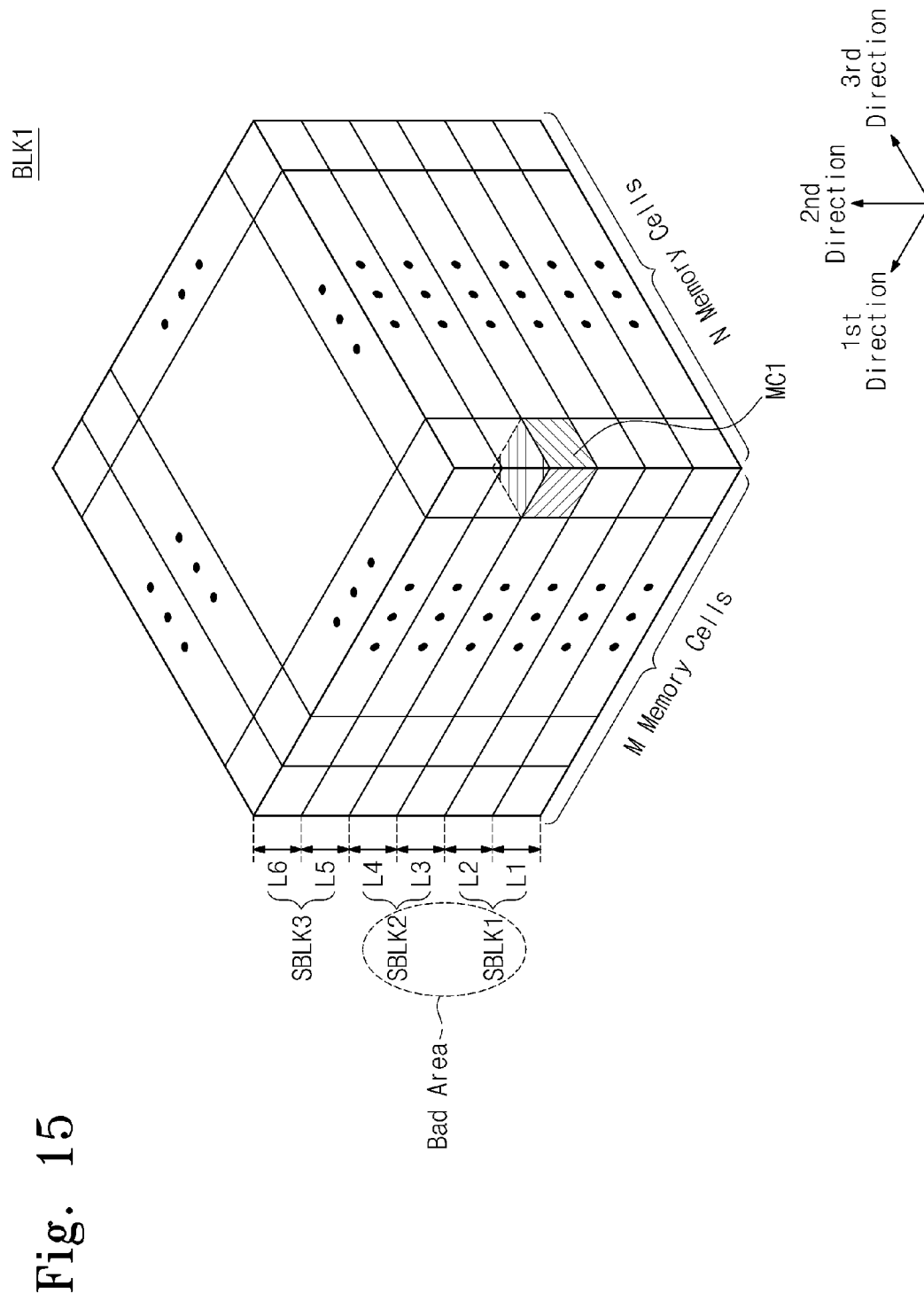


Fig. 16

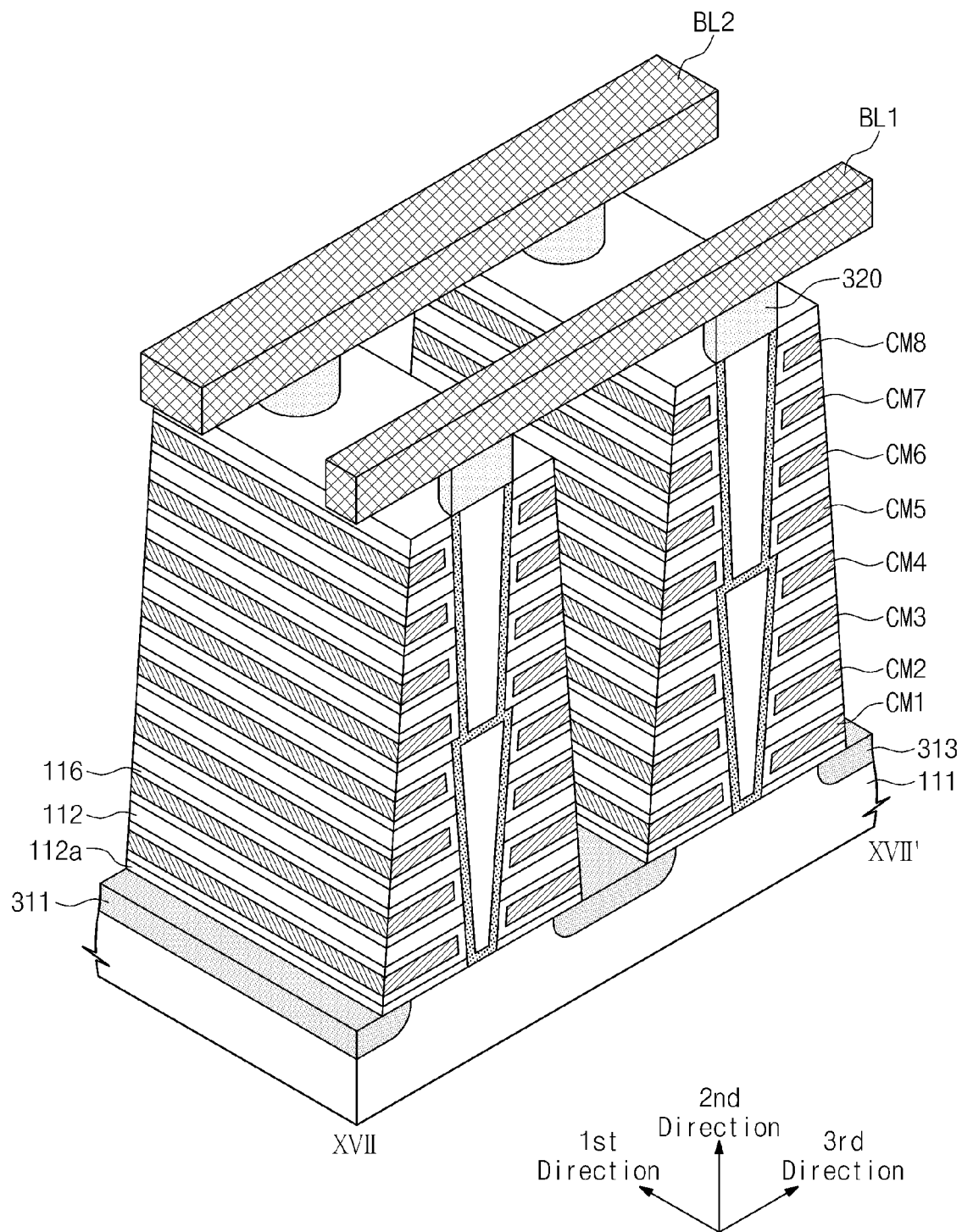


Fig. 18

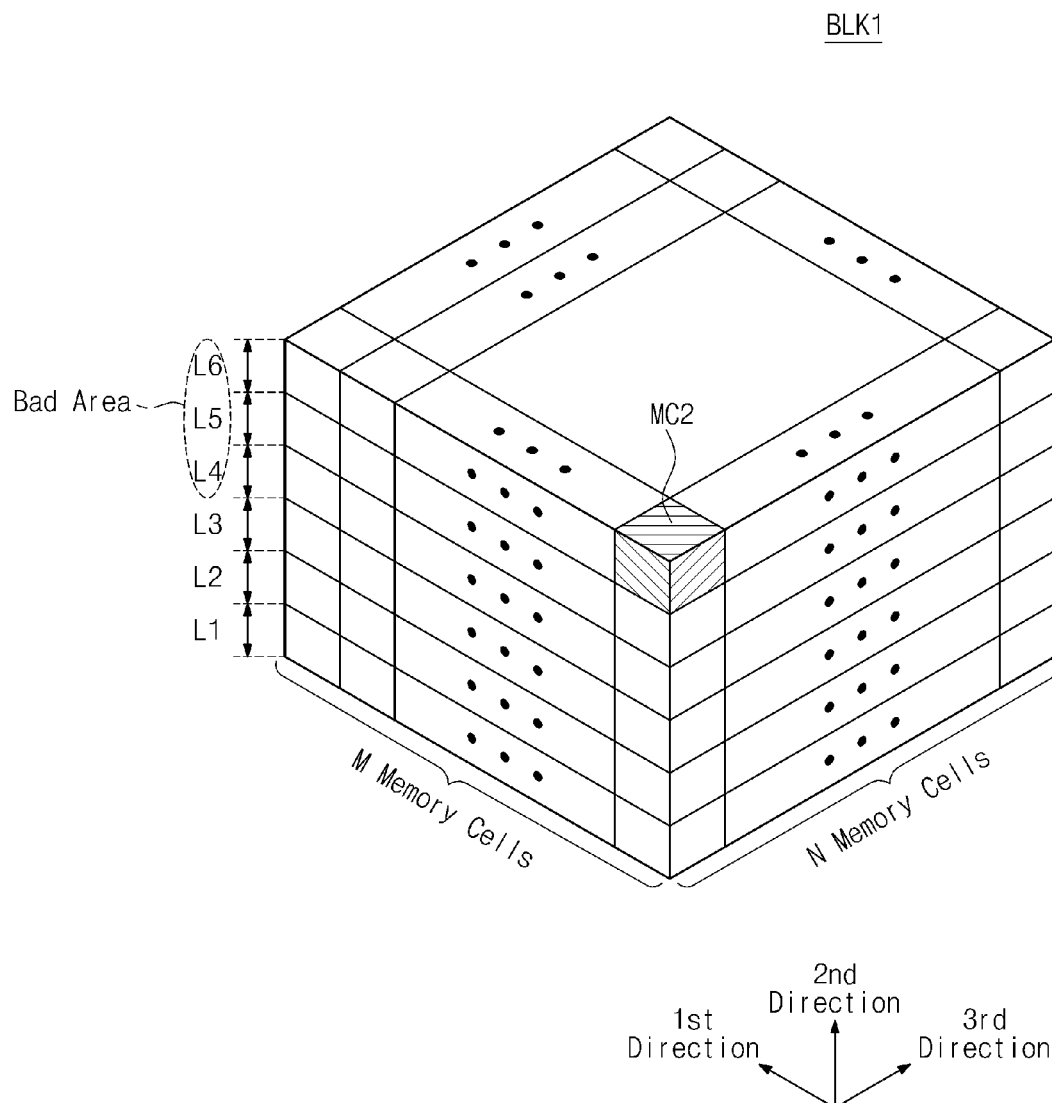


Fig. 19

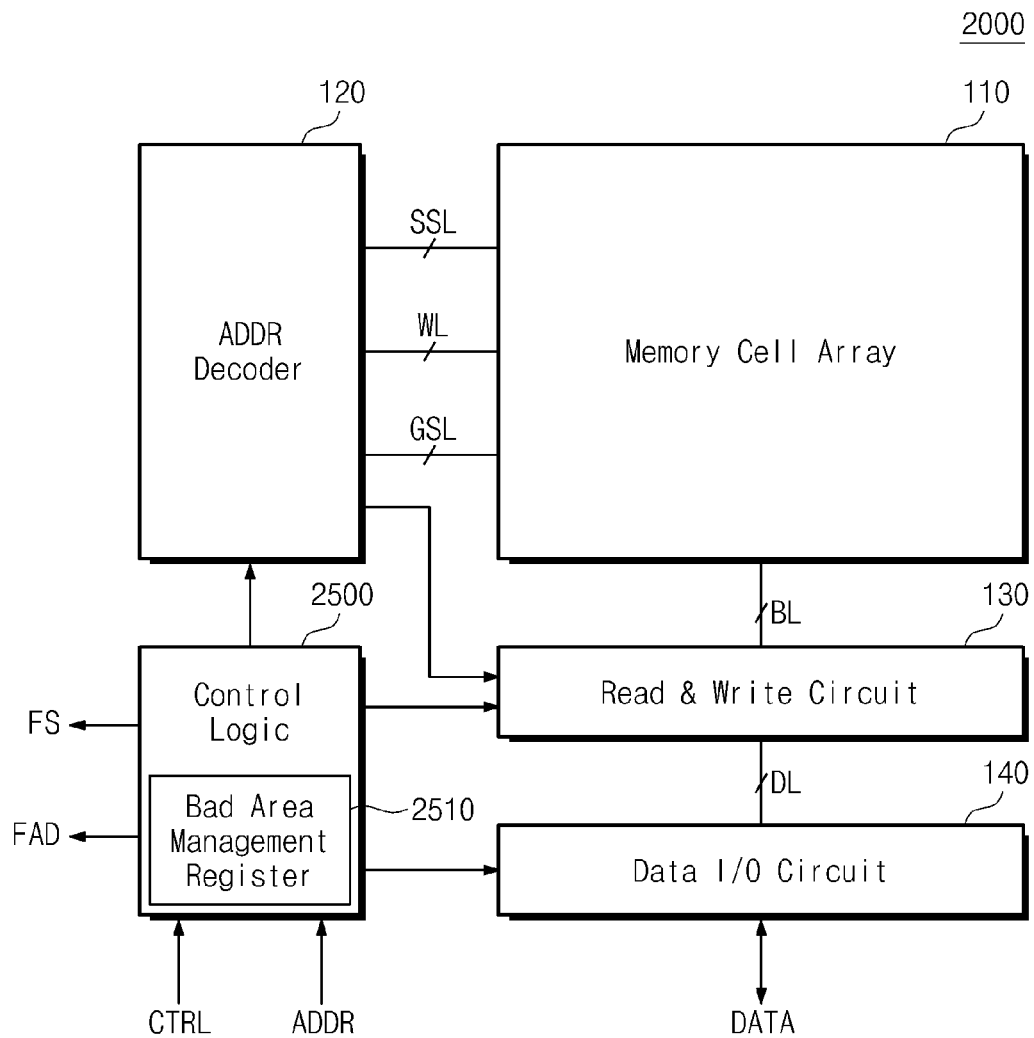


Fig. 20

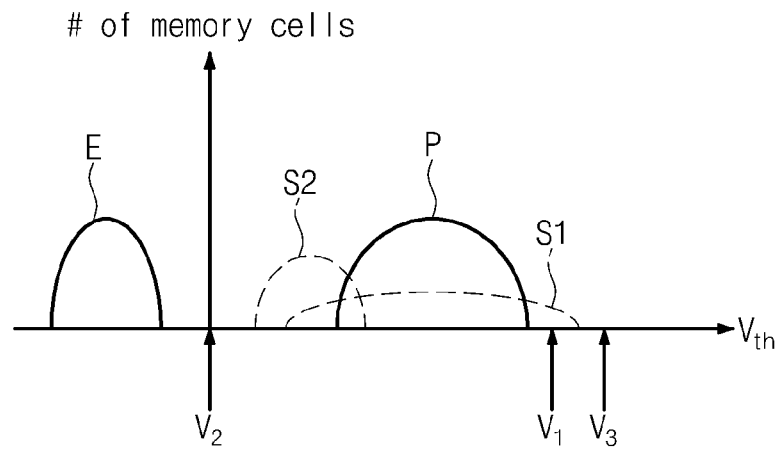


Fig. 21

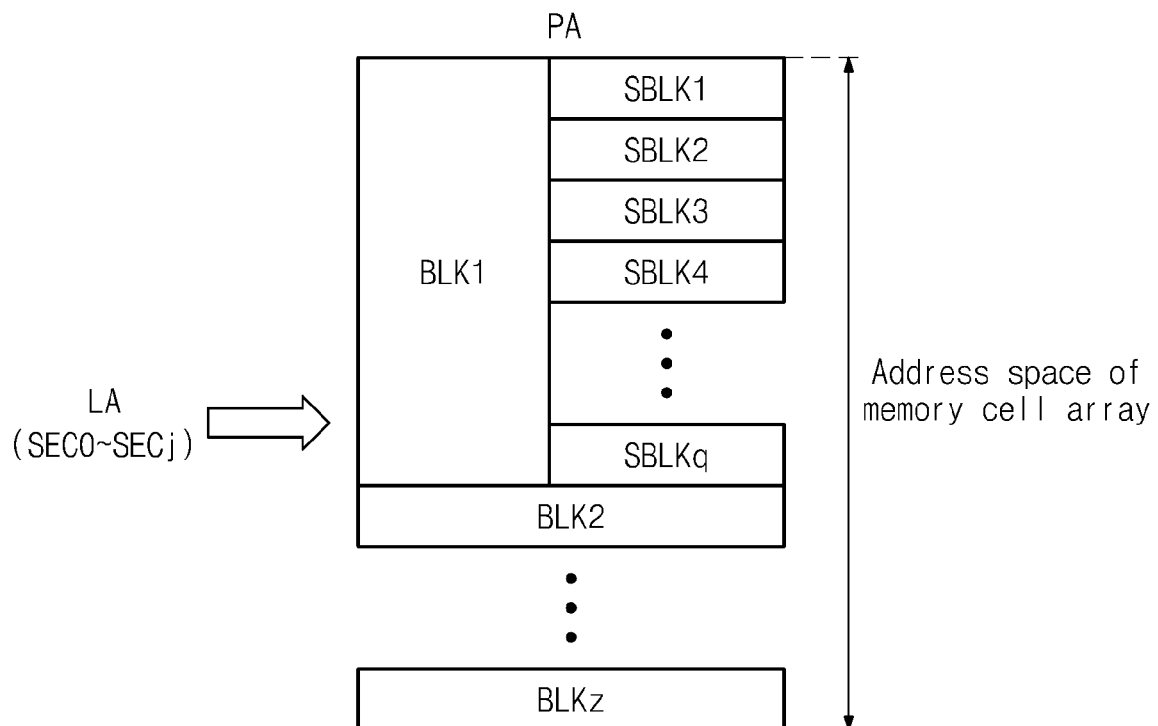


Fig. 22

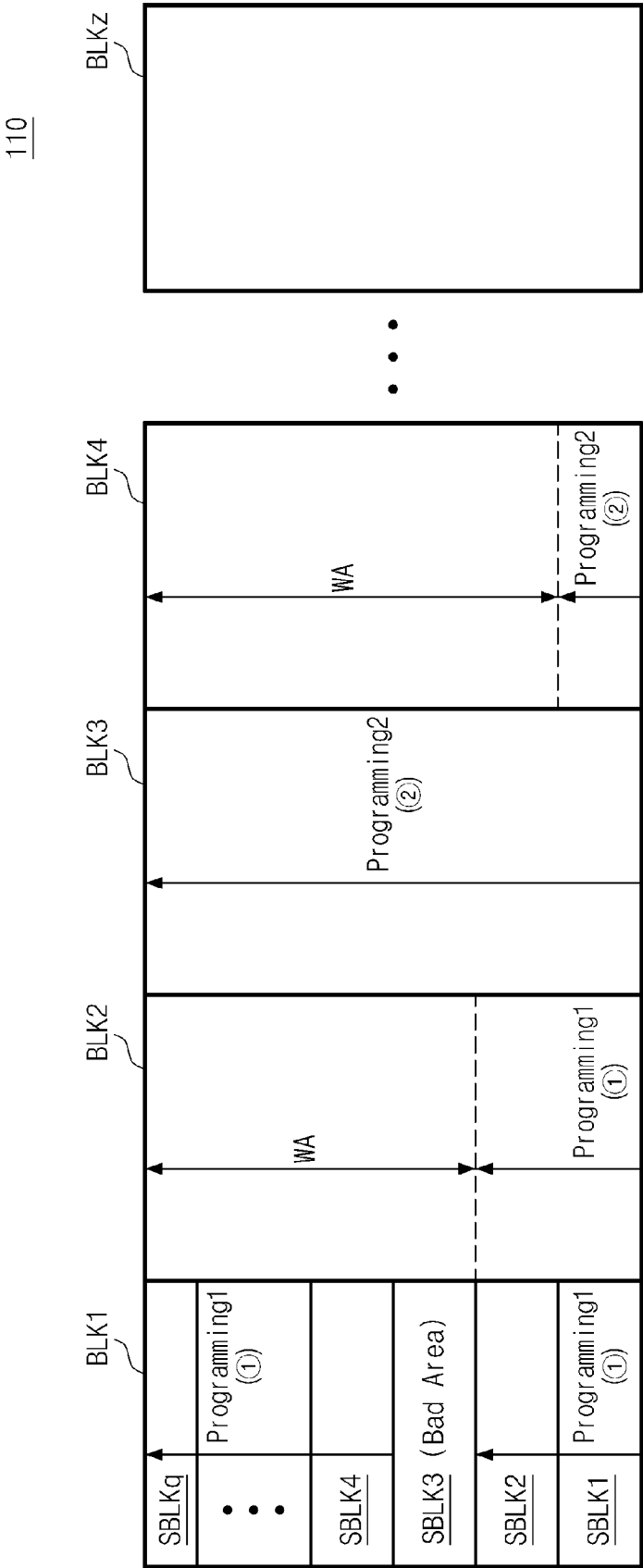


Fig. 23

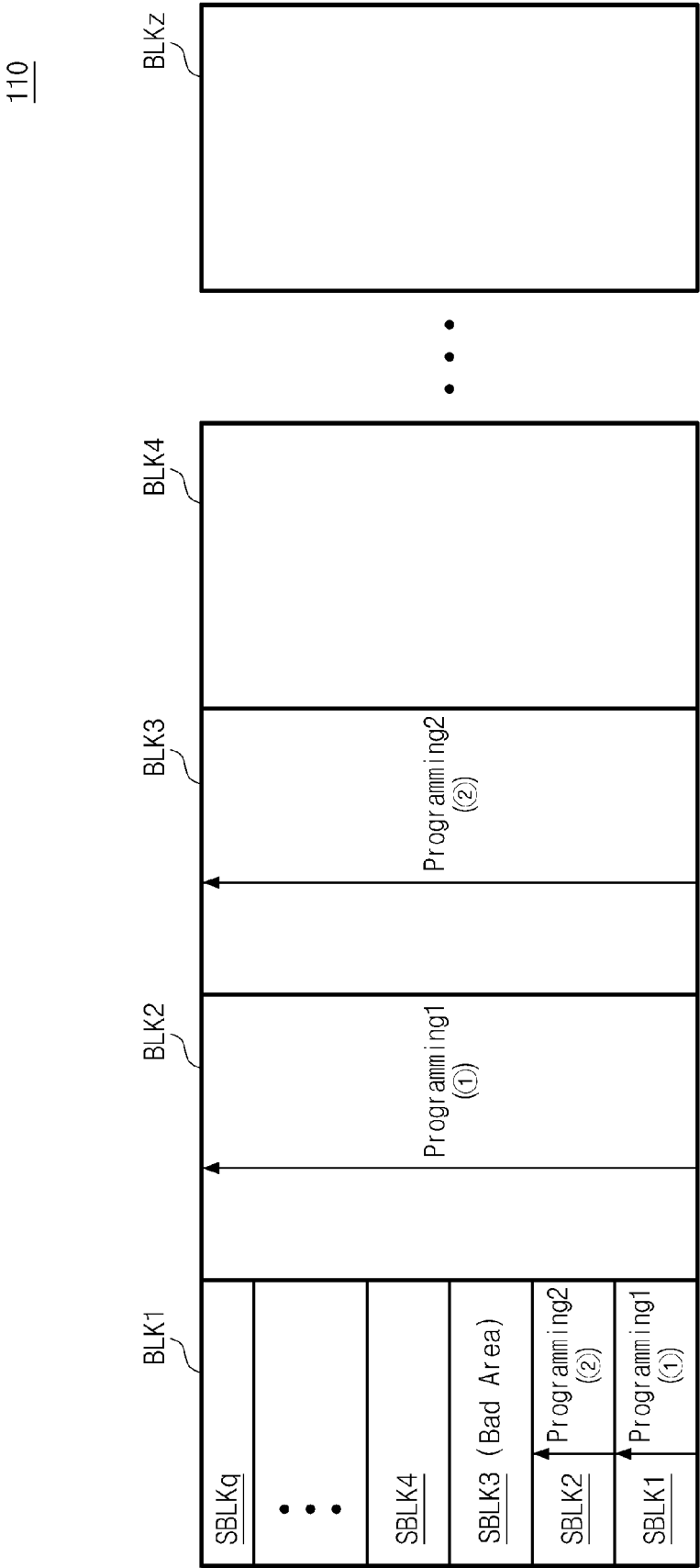


Fig. 24

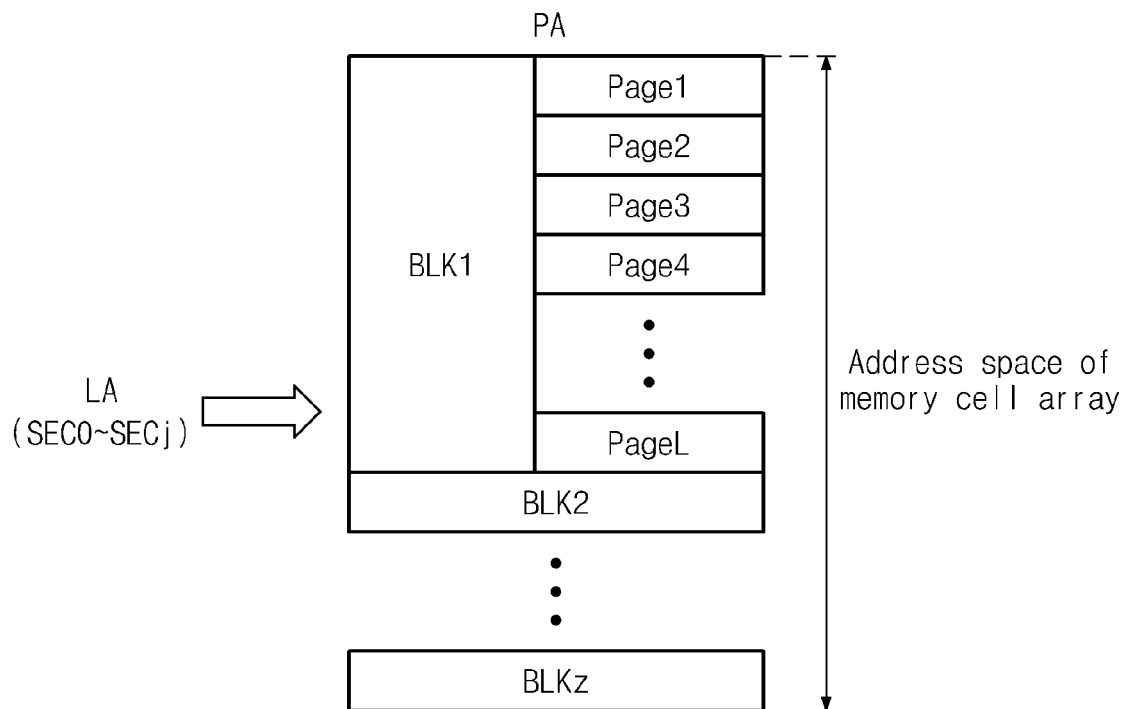
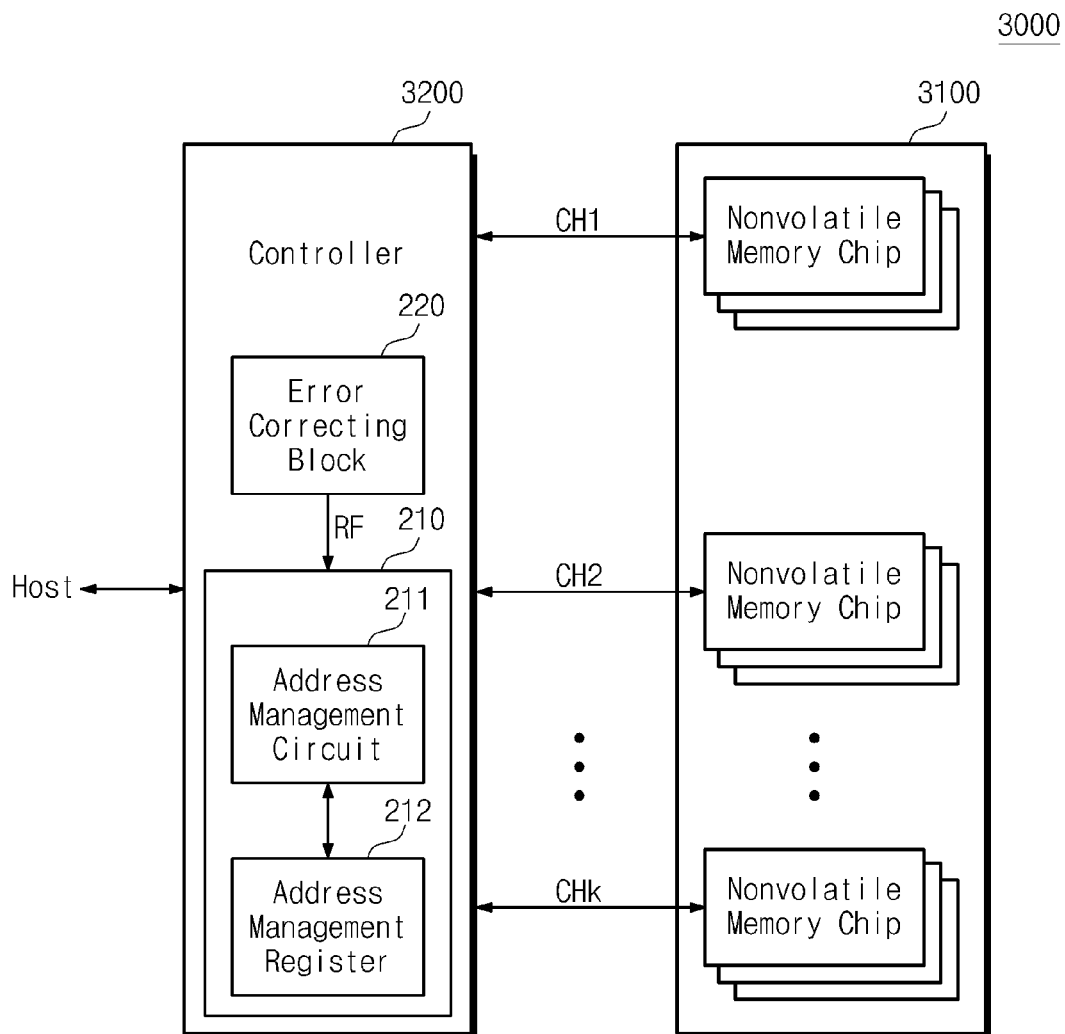


Fig. 25



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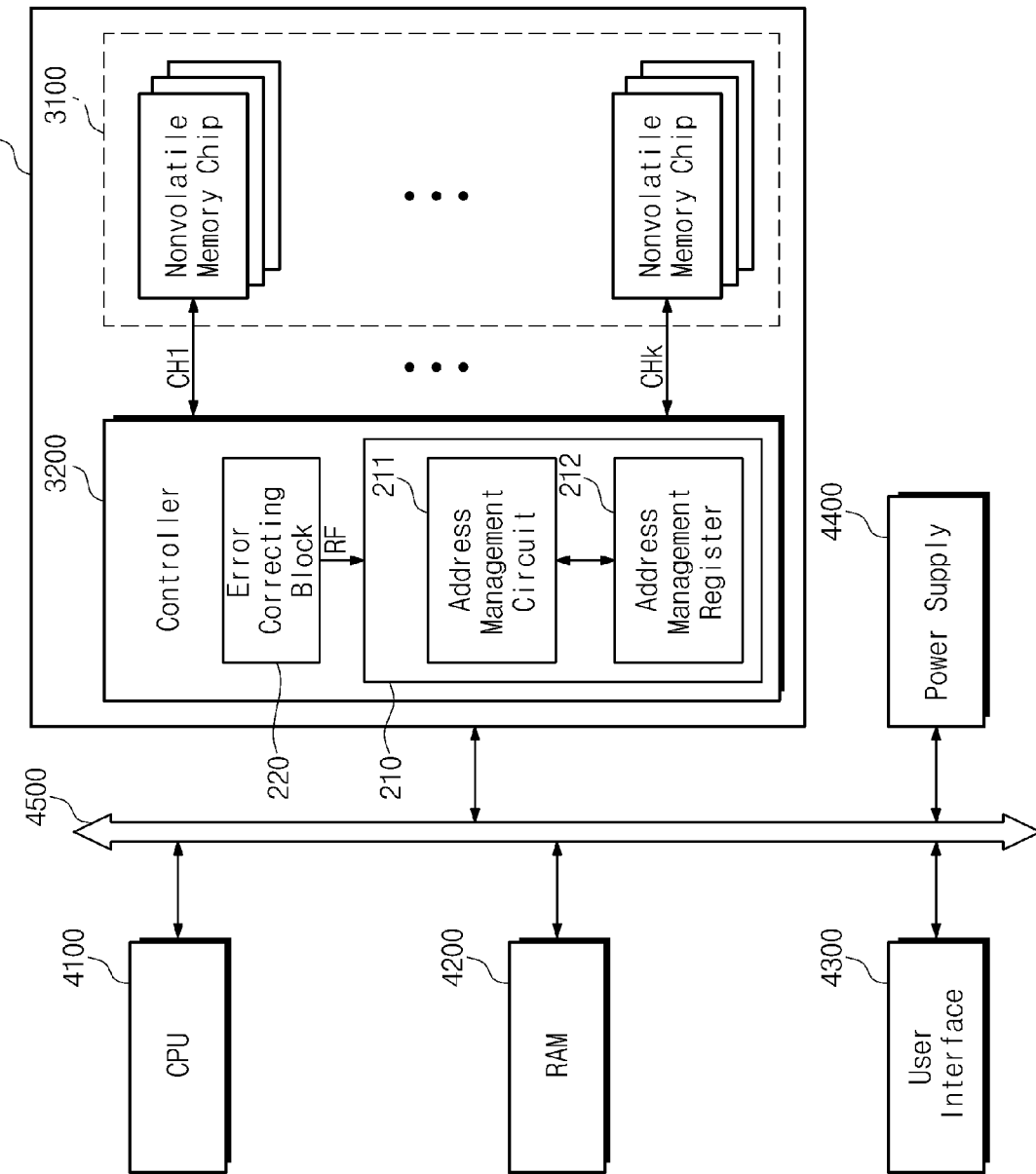


Fig. 26

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NONVOLATILE MEMORY DEVICE AND BAD AREA MANAGING METHOD THEREOF

CROSS-REFERENCE TO RELATED APPLICATIONS

This application claims foreign priority under 35 U.S.C. §119 to the benefit of Korean Patent Application No. 10-2011-0027730, filed Mar. 28, 2011, the entire disclosure of which is incorporated by reference herein.

BACKGROUND

Example embodiments relate to a nonvolatile memory device, and more particularly, relate to a bad area managing method of a nonvolatile memory device.

A semiconductor memory device may be fabricated using semiconductors such as silicon (Si), germanium (Ge), gallium arsenide (GaAs), indium phosphide (InP), and the like. Semiconductor memory devices may be classified as volatile memory devices and nonvolatile memory devices.

Volatile memory devices may lose stored contents when the power is off. Examples of volatile memory devices include static RAM (SRAM), dynamic RAM (DRAM), synchronous DRAM (SDRAM), and the like. Nonvolatile memory devices may retain stored contents even when their power is off. Nonvolatile memory devices include read only memory (ROM), programmable ROM (PROM), electrically programmable ROM (EPROM), electrically erasable and programmable ROM (EEPROM), flash memory, phase-change RAM (PRAM), magnetic RAM (MRAM), resistive RAM (RRAM), ferroelectric RAM (FRAM), and the like. Flash memory devices include NOR type and NAND type flash memory.

Semiconductor memory devices with a three-dimensional array structure are being developed. Semiconductor memory devices, including semiconductor memory devices with a three-dimensional array structure, may include some bad memory cells.

SUMMARY

According to example embodiments of inventive concepts, a bad area managing method of a nonvolatile memory device relates to a nonvolatile memory device including a plurality of memory blocks, each memory block containing memory layers stacked on a substrate. The bad area managing method includes accessing of the memory blocks, judging whether the accessed memory block includes at least one memory layer containing a bad memory cell. If the bad memory cell is detected, the method may include configuring the memory device to treat the at least one memory layer of the accessed memory block as a bad area.

The configuring the memory device to treat the at least one memory layer of the accessed memory block as a bad area may include treating a memory layer between the at least one memory layer containing the bad memory cell and the substrate, together with the at least one memory layer containing the bad memory cell, as a bad area.

The configuring the memory device to treat the at least one memory layer of the accessed memory block as a bad area may include treating all memory layers between the at least one memory layer containing the bad memory cell and the substrate, together with the memory layer including the bad memory cell, as a bad area.

Each memory layer may include a plurality of memory cells. Each memory block may include a semiconductor pillar

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that penetrates the memory layers of the memory block. The semiconductor pillar of each memory block may define channels of the plurality of memory cells contained within the memory block.

The configuring the memory device to treat the at least one memory layer of the accessed memory block as a bad area may include treating another memory layer other than the at least one memory layer containing the bad memory cell, together with the at least one memory layer containing the bad memory cell as a bad area. The semiconductor pillar may include a first width that is wider than a second width of the semiconductor pillar. The first width may correspond to the at least one memory layer containing the bad memory cell, and the second width may correspond to the another memory layer.

The plurality of memory layers in each memory block may be divided into a plurality of sub-memory blocks. The configuring the memory device to treat the at least one memory layer of the accessed memory block as a bad area may include treating at least one sub-memory block of the accessed memory block as a bad area, where the at least one sub-memory block may contain the bad memory cell.

The configuring the memory device to treat the at least one memory layer of the accessed memory block as a bad area may include treating another sub-memory block other than the sub-memory block containing the bad memory cell, together with the sub-memory block containing the bad memory cell, as a bad area. The sub-memory block may include a semiconductor pillar that penetrates the memory layers of the sub-memory block. The semiconductor pillar may include a first width that is wider than a second width of the semiconductor pillar. The first width may correspond to the sub-memory block containing the bad memory cell. The second width may correspond to the another sub-memory block.

Each memory block may include a plurality of memory cells and a semiconductor pillar, the semiconductor pillar penetrating the memory layers of the memory block. The semiconductor pillar of each memory block may define channels of memory cells contained within the memory block. The semiconductor pillar may include first and second sub semiconductor pillars that are perpendicular to the substrate and the first sub semiconductor pillar penetrates the at least one memory layer including the bad memory cell. A first width of the first sub semiconductor pillar may be wider than a second width of the first sub semiconductor pillar. The first width may correspond to the at least one sub-memory layer including the bad memory cell and the second width may correspond to the at least one sub-memory layer. The configuring the memory device to treat the at least one memory layer of the accessed memory block as a bad area may include treating another memory layer penetrated by the first sub semiconductor pillar, together with the at least one memory layer containing the bad memory cell, as a bad area.

Each memory layer may include a plurality of memory cells. Each memory block may include a plurality of word lines connected to the plurality of memory layers contained within the memory block, respectively. At a program or read operation, memory cells connected with a selected word line may be accessed by applying a first voltage to the selected word line and applying a second voltage to unselected word lines, or by applying a first voltage to the selected word line, applying a second voltage to unselected word lines, and applying a third voltage to word lines connected with the bad area, the third voltage being higher in level than the second voltage.

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According to example embodiments of inventive concepts, a nonvolatile memory device includes a nonvolatile memory portion including a plurality of memory blocks, and each of the plurality of memory blocks may contain memory layers stacked on a substrate. The device may further include a controller configured to manage at least one memory layer of an accessed one of the plurality of memory blocks as a bad area when the memory device detects a bad memory cell in the least one memory layer of the accessed memory block.

The controller may include an address management register configured to store bad area information about the bad area, and an address management circuit configured to update the bad area information such that the at least one memory layer including the bad memory cell is managed as the bad area.

The address management circuit may be configured to provide a physical address based upon the bad area information, the nonvolatile memory portion being accessed according to the physical address. At a program or read operation, the address management circuit may be configured to provide the physical address by a page unit when the memory block including the bad area is selected and by a memory block unit when a memory block not including the bad area is selected.

Memory layers included in each memory block may be divided into a plurality of sub-memory blocks stacked on the substrate, and the controller may include an address management register configured to store bad area about the bad area, and an address management circuit configured to update the bad area information such that the at least one sub-memory block including the bad memory cell is managed as the bad area.

The address management circuit may be configured to provide a physical address based upon the bad area information. The nonvolatile memory portion may be configured to be accessed according to the physical address. At a program or read operation, the address management circuit may be configured to provide the physical address by a sub-memory block unit when a memory block including the bad area is selected and by a memory block unit when a memory block not including the bad area is selected.

The controller may be configured to treat another memory layer other than the at least one memory layer including the bad memory cell, together with the at least one memory layer including the bad memory cell, as a bad area. Each memory cell may include a semiconductor pillar which is formed to penetrate memory layers included in each memory block and provides channels to memory cells of each memory block, a first width of the semiconductor pillar is wider than a second width of the semiconductor pillar, and the first width corresponds to a memory layer including the bad memory cell and the second width corresponds to the another memory layer.

According to example embodiments, a nonvolatile memory device includes a nonvolatile memory portion including a plurality of memory blocks. Each memory block may include at least one cell string containing a plurality of cell transistors stacked on a substrate. Each cell string may include a semiconductor pillar that penetrates the plurality of cell transistors. The device may further include a controller configured to manage a bad area of the nonvolatile memory portion when the memory device detects a bad cell transistor in one of the plurality of memory blocks.

The controller may be configured to detect the bad area of the nonvolatile memory portion in response to receiving at least one of a read fail signal, a program fail signal, and an erase fail signal when at least one of the plurality of memory blocks is accessed by the controller.

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Each memory block may include a plurality of sub-memory blocks. Each sub-memory block may contain at least one row of cell transistor in the memory block. The controller may be configured to manage the bad area of the nonvolatile memory portion during a first programming operation by storing data of the first programming operation in a first-sub memory block of a first memory block, and storing data of the first programming operation in at least one other memory block when the memory device detects the first memory block includes another sub-memory block containing a bad cell transistor and the other memory block does not contain a bad cell transistor.

The controller may be configured to manage the bad area of the nonvolatile memory portion during a second programming operation by storing data of the second programming operation in at least one different memory block when the memory device detects the first memory block includes another sub-memory block containing a bad cell transistor and at least one different memory block does not contain a bad cell transistor.

According to example embodiments, a computing system may include a CPU connected via a system bus to the foregoing nonvolatile memory device.

BRIEF DESCRIPTION OF THE FIGURES

The foregoing and other features and advantages of inventive concepts will become apparent from the following description of non-limiting embodiments, as illustrated in the following figures in which like reference numerals refer to like parts throughout the various figures unless otherwise specified. The drawings are not necessarily to scale, emphasis instead being placed upon illustrating the principles of inventive concepts. In the drawings:

FIG. 1 is a block diagram illustrating a nonvolatile memory device coupled with a host.

FIG. 2 is a block diagram illustrating a nonvolatile memory portion according to example embodiments of inventive concepts.

FIG. 3 is a diagram illustrating a memory cell array in FIG. 2.

FIG. 4 is a perspective view of one of memory blocks in FIG. 3.

FIG. 5 is a cross-sectional view taken along a line V-V' in FIG. 4.

FIG. 6 is a diagram illustrating one of the cell transistors in FIG. 5.

FIG. 7 is a circuit diagram illustrating an equivalent circuit of a memory block.

FIG. 8 is a flowchart illustrating a bad area managing method of a nonvolatile memory device in FIG. 1.

FIG. 9 is a diagram conceptually illustrating memory cells of a memory block.

FIG. 10 is a diagram illustrating an address management register in FIG. 1.

FIG. 11 is a flowchart illustrating a bad area managing method according to example embodiments of inventive concepts.

FIG. 12 is a diagram for describing the case that third and fourth memory layers are treated as a bad area.

FIG. 13 is a diagram for describing the case that first to fourth memory layers are treated as a bad area.

FIG. 14 is a diagram for describing the case that second sub-memory layer is treated as a bad area.

FIG. 15 is a diagram for describing the case that first and second sub-memory layers are treated as a bad area.

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FIG. 16 is a perspective view illustrating a memory block in FIG. 3 according to example embodiments of inventive concepts.

FIG. 17 is a cross-sectional view of a memory block taken along a line XVII-XVII'.

FIG. 18 is a diagram conceptually illustrating memory cells of a memory block in FIGS. 16 and 17.

FIG. 19 is a block diagram illustrating a nonvolatile memory portion according to example embodiments of inventive concepts.

FIG. 20 is a diagram illustrating a threshold voltage distribution of memory cells in a memory cell array in FIG. 19.

FIG. 21 is a diagram for describing a mapping relationship between physical addresses and logical addresses according to example embodiments of inventive concepts.

FIG. 22 is a diagram for describing a method of storing data in a first memory block including a bad area according to a mapping relationship described in FIG. 21, according to example embodiments.

FIG. 23 is a diagram for describing a method of storing data in a first memory block including a bad area according to a mapping relationship described in FIG. 21, according to example embodiments.

FIG. 24 is a diagram for describing a mapping relationship between physical addresses and logical addresses according to example embodiments of inventive concepts.

FIG. 25 is a block diagram illustrating an application of a nonvolatile memory device in FIG. 1.

FIG. 26 is a block diagram illustrating a computing system including a nonvolatile memory device in FIG. 25.

DETAILED DESCRIPTION

Example embodiments of inventive concepts will be described more fully hereinafter with reference to the accompanying drawings, in which some example embodiments of inventive concept are shown. Example embodiments of inventive concepts may, however, be embodied in many different forms and should not be construed as limited to the embodiments set forth herein. Rather, these example embodiments are provided so that this disclosure will be thorough and complete, and will fully convey the scope of inventive concepts to those of ordinary skill in the art. In the drawings, the size and relative sizes of layers and regions may be exaggerated for clarity. Like numbers refer to like elements throughout, and thus their description will be omitted.

It will be understood that, although the terms first, second, third etc. may be used herein to describe various elements, components, regions, layers and/or sections, these elements, components, regions, layers and/or sections should not be limited by these terms. These terms are only used to distinguish one element, component, region, layer or section from another region, layer or section. Thus, a first element, component, region, layer or section discussed below could be termed a second element, component, region, layer or section without departing from the teachings of the inventive concept.

Spatially relative terms, such as "beneath", "below", "lower", "under", "above", "upper" and the like, may be used herein for ease of description to describe one element or feature's relationship to another element(s) or feature(s) as illustrated in the figures. It will be understood that the spatially relative terms are intended to encompass different orientations of the device in use or operation in addition to the orientation depicted in the figures. For example, if the device in the figures is turned over, elements described as "below" or "beneath" or "under" other elements or features would then

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be oriented "above" the other elements or features. Thus, the exemplary terms "below" and "under" can encompass both an orientation of above and below. The device may be otherwise oriented (rotated 90 degrees or at other orientations) and the spatially relative descriptors used herein interpreted accordingly. In addition, it will also be understood that when a layer is referred to as being "between" two layers, it can be the only layer between the two layers, or one or more intervening layers may also be present.

The terminology used herein is for the purpose of describing particular embodiments only and is not intended to be limiting of example embodiments of inventive concepts. As used herein, the singular forms "a", "an" and "the" are intended to include the plural forms as well, unless the context clearly indicates otherwise. It will be further understood that the terms "comprises" and/or "comprising," when used in this specification, specify the presence of stated features, integers, steps, operations, elements, and/or components, but do not preclude the presence or addition of one or more other features, integers, steps, operations, elements, components, and/or groups thereof. As used herein, the term "and/or" includes any and all combinations of one or more of the associated listed items.

It will be understood that when an element or layer is referred to as being "on", "connected to", "coupled to", or "adjacent to" another element or layer, it can be directly on, connected, coupled, or adjacent to the other element or layer, or intervening elements or layers may be present. In contrast, when an element is referred to as being "directly on," "directly connected to", "directly coupled to", or "immediately adjacent to" another element or layer, there are no intervening elements or layers present.

Example embodiments are described herein with reference to cross-sectional illustrations that are schematic illustrations of idealized embodiments (and intermediate structures) of example embodiments. As such, variations from the shapes of the illustrations as a result, for example, of manufacturing techniques and/or tolerances, are to be expected. Thus, example embodiments should not be construed as limited to the particular shapes of regions illustrated herein but are to include deviations in shapes that result, for example, from manufacturing. Thus, the regions illustrated in the figures are schematic in nature and their shapes are not intended to illustrate the actual shape of a region of a device and are not intended to limit the scope of example embodiments.

Unless otherwise defined, all terms (including technical and scientific terms) used herein have the same meaning as commonly understood by one of ordinary skill in the art to which this inventive concept belongs. It will be further understood that terms, such as those defined in commonly used dictionaries, should be interpreted as having a meaning that is consistent with their meaning in the context of the relevant art and/or the present specification and will not be interpreted in an idealized or overly formal sense unless expressly so defined herein.

FIG. 1 is a block diagram illustrating a nonvolatile memory device coupled with a host. Referring to FIG. 1, a nonvolatile memory device 1000 includes a nonvolatile memory portion 100 and a controller 200. The nonvolatile memory portion 100 includes a memory cell array 110. The nonvolatile memory device 1000 stores data in the memory cell array 110 and sends data stored in the memory cell array 110 to a host.

The memory cell array 110 includes a substrate and a plurality of memory blocks although not shown in FIG. 1. Each of the memory blocks includes a plurality of sub blocks. Each sub block includes memory layers stacked on the substrate. Each memory layer includes a plurality of memory

cells arranged in a direction parallel with the substrate. This will be more fully described with reference to FIGS. 3 to 7.

The controller **200** is coupled with a host and the nonvolatile memory portion **100**. The controller **200** is configured to access the nonvolatile memory portion **100** in response to a request from a host. The controller **200** communicates with the nonvolatile memory portion **100** via one channel CH. The controller **200** transfers a control signal CTRL, exchanges data, and receives a fail signal FS and a fail address FAD, which are performed via the channel CH.

The controller **200** is configured to control read, program, erase, and background operations of the nonvolatile memory portion **100**, for example. The controller **200** is configured to provide an interface between the nonvolatile memory portion **100** and the host. The controller **200** is configured to drive firmware for controlling the nonvolatile memory portion **100**.

The controller **200** is configured to provide the control signals CTRL and the address ADDR to the nonvolatile memory portion **100**. The nonvolatile memory portion **100** may perform read, program, and erase operations according to the control signal CTRL. The nonvolatile memory portion **100** reads data from an area corresponding to the address ADDR, programs data in the area corresponding to the address ADDR, or erases the area corresponding to the address ADDR.

The controller includes a flash translation layer (FTL) **210** and an error correcting block **220**. The FTL **210** may manage a bad area of the memory cell array **110**. The bad area is an area of which the reliability is judged to be low, and memory cells included in the bad area are not used.

The FTL **210** includes an address management circuit **211** and an address management register **212**. The address management circuit **211** translates a logical address input from the host into a physical address. A mapping table storing a mapping relationship between logical addresses and physical addresses is stored in the address management register **212**.

The controller **200** provides the nonvolatile memory portion **100** with the address ADDR based upon the translated physical address. For example, a logical address can be translated into a physical address of a memory block unit. This is referred to as block mapping. In this case, the controller **200** sequentially provides the nonvolatile memory portion **100** with addresses ADDR of pages included within a memory cell to be accessed. As another example, in case of the block mapping, the address management circuit **211** provides offset information with a physical address. The offset information means a difference between an address of a first page within a memory block to be accessed or an address of a specific page and an address of a page to be accessed. The controller **200** may provide addresses ADDR of pages included within a memory block to be accessed sequentially according to the offset information.

At programming and reading, the address ADDR may correspond to any page included within the memory cell array **110**. At erasing, the address ADDR may correspond to any memory block included within the memory cell array **110**. An erase operation is performed by the memory block. Alternatively, the erase operation is performed by a sub-memory block.

A logical address can be translated into a physical address of a page unit. This is referred to as page mapping. In this case, the controller **200** provides the nonvolatile memory portion **100** with a physical address translated by the FTL **210** as an address ADDR illustrated in FIG. 1.

According to an example embodiments of inventive concepts, the address management circuit **211** manages a bad area by a memory layer unit or a sub-memory block unit, not

a memory block unit. For example, the address management circuit **211** manages the bad area by a memory layer unit or a sub-memory block unit, regardless of whether an erase operation is executed by a memory block unit or by a sub-memory block unit.

The address management circuit **211** provides a physical address and simultaneously stores it in the address management register **212**. In the event that a bad memory cell is generated, the address management circuit **211** judges at least one memory layer including the bad memory cell to be a bad area. Information (hereafter, referred to as bad area information) about the judged bad area is stored in the address management register **212**. Generation of a bad memory cell means that erasing, reading, or programming about an area corresponding to a physical address stored in the address management register **211** is failed.

At programming, the nonvolatile memory portion **100** may provide the controller **200** with a fail signal FS indicating that a program operation is failed. In response to the fail signal FS, the address management circuit **211** treats a memory layer including a program-failed page as a bad area, based upon a temporarily stored physical address.

At reading, the error correcting block **220** is configured to detect and correct erroneous bits of data read out from the nonvolatile memory portion **100** using an error correcting code (ECC).

At reading, the error correcting block **220** can correct a limited number of erroneous bits. In the event that erroneous bits exceeding the limited number exist at a selected page, the error correcting block **220** does not correct the erroneous bits. If the number of erroneous bits exceeds the limited number, the error correcting block **220** generates a read fail signal RF.

In response to the read fail signal RF, the address management circuit **211** detects that the selected page includes bad memory cells. For example, the address management circuit **211** detects the selected page by referring to a mapping table storing a mapping relationship between logical addresses and physical addresses. The address management circuit **211** treats a memory layer including the selected page as a bad area.

At erasing the controller **200** receives a fail address FAD indicating an address of a page including an erase-failed memory cell (or, a bad memory cell) from the nonvolatile memory portion **100**. The address management circuit **211** treats a memory layer including the erase-failed page as a bad area based upon the fail address FAD.

At programming and reading, the address management circuit **211** may translate a logical address into a physical address, based upon bad area information stored in the address management register **212**. This means that the address management circuit **211** translates a logical address into a physical address corresponding to a normal area, not a bad area.

According to example embodiments, the bad area information may be stored in the memory cell array **110** of the nonvolatile memory portion **100**. Whenever the bad area information is updated, the updated bad area information can be stored in the memory cell array **110** of the nonvolatile memory portion **100**. The bad area information may be stored in a desired (or alternatively predetermined area) of the memory cell array **110**. For example, the bad area information may be stored in a part of a first memory block BLK1 of the memory cell array **110** in FIG. 2, but example embodiments are not limited thereto.

The address management circuit **211** loads bad area information stored in the memory cell array **110** and manages the bad area information. For example, when the nonvolatile

memory device **1000** is powered off, the bad area information stored in the address management register **212** may be stored in the nonvolatile memory portion **100**. When the nonvolatile memory device **1000** is powered up, the bad area information stored in the nonvolatile memory portion **100** may be loaded onto the address management register **212**.

The controller **200** may further include a RAM, a processing unit, a host interface, and a memory interface. The RAM may be used as at least one of a cache memory between the nonvolatile memory portion **100** and the host or a buffer memory between the nonvolatile memory portion **100** and the host. Alternatively, the RAM can be used as the address management register **212**.

The processing unit controls an overall operation of the controller **200**. For example, the processing unit may perform a function of the address management circuit **211**.

The host interface may include the protocol for executing data exchange between the host and the controller **200**. The host interface may communicate with an external device (e.g., the host) via at least one of various protocols such as an USB (Universal Serial Bus) protocol, an MMC (multimedia card) protocol, a PCI (peripheral component interconnection) protocol, a PCI-E (PCI-express) protocol, an ATA (Advanced Technology Attachment) protocol, a Serial-ATA protocol, a Parallel-ATA protocol, a SCSI (small computer small interface) protocol, an ESDI (enhanced small disk interface) protocol, and an IDE (Integrated Drive Electronics) protocol, but example embodiments are not limited thereto. The host interface **124** can communicate with the host using the proprietary interface instead of the above-described protocols. The memory interface interfaces with the nonvolatile memory portion **200**. The memory interface includes a NAND interface or a NOR interface.

The controller **200** and the nonvolatile memory portion **100** may be integrated in a single semiconductor device. The controller **200** and the nonvolatile memory portion **100** may be integrated in a single semiconductor device to form a memory card. For example, the controller **200** and the nonvolatile memory portion **100** may be integrated in a single semiconductor device to form a memory card such as a PC (PCMCIA) card, a CF card, an SM (or, SMC) card, a memory stick, a multimedia card (MMC, RS-MMC, MMCmicro), a security card (SD, miniSD, microSD, SDHC), a universal flash storage (UFS) device, or the like, but example embodiments are not limited thereto.

The controller **200** and the nonvolatile memory portion **100** may be integrated in a single semiconductor device to form a solid state drive (SSD). The SSD includes a storage device configured to store data in a semiconductor memory. If the nonvolatile memory device **1000** is used as the SSD, it is possible to remarkably improve an operating speed of a host coupled with the nonvolatile memory device **1000**.

According to example embodiments, the nonvolatile memory device **1000** may be used as computer, portable computer, Ultra Mobile PC (UMPC), workstation, net-book, PDA, web tablet, wireless phone, mobile phone, smart phone, e-book, PMP (portable multimedia player), digital camera, digital audio recorder/player, digital picture/video recorder/player, portable game machine, navigation system, black box, 3-dimensional television, a device capable of transmitting and receiving information at a wireless circumstance, one of various electronic devices constituting home network, one of various electronic devices constituting computer network, one of various electronic devices constituting telematics network, RFID, or one of various electronic devices constituting a computing system, but example embodiments are not limited thereto.

According to example embodiments, the nonvolatile memory portion **110** or the nonvolatile memory device **1000** may be packed by various types of packages such as PoP (Package on Package), Ball grid arrays (BGAs), Chip scale packages (CSPs), Plastic Leaded Chip Carrier (PLCC), Plastic Dual In-Line Package (PDI2P), Die in Waffle Pack, Die in Wafer Form, Chip On Board (COB), Ceramic Dual In-Line Package (CERDIP), Plastic Metric Quad Flat Pack (MQFP), Thin Quad Flatpack (TQFP), Small Outline (SOIC), Shrink Small Outline Package (SSOP), Thin Small Outline (TSOP), Thin Quad Flatpack (TQFP), System In Package (SIP), Multi Chip Package (MCP), Wafer-level Fabricated Package (WFP), Wafer-Level Processed Stack Package (WSP), and the like, but example embodiments are not limited thereto.

FIG. **2** is a block diagram illustrating a nonvolatile memory portion according to example embodiments of inventive concepts. Referring to FIG. **2**, a nonvolatile memory portion **100** includes a memory cell array **110**, an address decoder **120**, a read/write circuit **130**, a data input/output circuit **140**, and control logic **150**.

The memory cell array **110** includes a plurality of memory blocks BLK1 to BLKz. Each memory block includes a plurality of memory layers stacked on a substrate. The plurality of memory layers may be stacked along a direction perpendicular to the substrate. Each memory layer includes a plurality of memory cells arranged on the substrate in row and column directions. That is, the memory cells are arranged on the substrate in row and column directions and stacked along a direction perpendicular to the substrate, so that they form a three-dimensional structure. The memory cell array **110** includes memory cells, each storing one or more bits of data.

The address decoder **120** is configured to operate in response to the control of the control logic **150**. The address decoder **120** receives an address ADDR from the control logic **150**.

The address decoder **120** decodes a block address of the input address ADDR. At least one memory block may be selected according to the decoded block address. The address decoder **120** decodes a row address of the input address ADDR. The address decoder **120** is configured to select a word line WL corresponding to the decoded row address. The address decoder **120** is configured to select a string selection line SSL and a ground selection line GSL corresponding to the decoded row address among string selection lines SSL and ground selection lines GSL. The address decoder **120** may select a line corresponding to the row address by applying different voltages to a selected word line and unselected word lines.

The address decoder **120** is configured to decode a column address of the input address ADDR. The address decoder **120** transfers the decoded column address DCA to the read/write circuit **130**.

According to example embodiments, the address decoder **120** may include a row decoder configured to decode a row address, a column decoder configured to decode a column address, an address buffer configured to store an address ADDR, and the like.

The read/write circuit **130** may be coupled with the memory cell array **110** via bit lines BL. The read/write circuit **130** is configured to exchange data with the data input/output circuit **140**. The read/write circuit **130** operates responsive to the control of the control logic **150**. The read/write circuit **130** receives the decoded column address DCA from the address decoder **120**. The read/write circuit **130** selects a part of the bit lines BL in response to the decoded column address DCA.

The read/write circuit **130** is configured to receive data and to write it in the memory cell array **110**. The read/write circuit

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130 is configured to read data from the memory cell array 110 and to output it to the data input/output circuit 140. The read/write circuit 130 is configured to read data from a first storage area of the memory cell array 110 and to write it in a second storage area thereof. That is, the read/write circuit 130 performs a copy-back operation.

The read/write circuit 130 may include constituent elements such as a page buffer (or, a page register), a column selector circuit, a data buffer, and the like. Alternatively, the read/write circuit 130 may include constituent elements such as a sense amplifier, a write driver, a column selector circuit, a data buffer, and the like.

The data input/output circuit 140 is coupled with the read/write circuit 130 via data lines DL. The data input/output circuit 140 operates responsive to the control of the control logic 150. The data input/output circuit 140 is configured to exchange data with an external device. The data input/output circuit 140 is configured to transfer data from the external device into the read/write circuit 130 via the data lines DL. The data input/output circuit 140 is configured to output data transferred from the read/write circuit 130 via the data lines DL to the external device. For example, the data input/output circuit 140 includes a data buffer.

The control logic 150 is coupled with the address decoder 120, the read/write circuit 130, and the data input/output circuit 140. The control logic 150 is configured to control an overall operation of the nonvolatile memory portion 100 in response to a control signal CTRL input from a controller 200. The control logic 150 provides the input address ADDR to the address decoder 120.

At programming, an incremental step pulse programming (ISPP) manner may be used. With the ISPP manner, a program voltage stepwise increased may be applied to a selected word line. This enables threshold voltages of memory cells to be programmed to increase. Afterwards, a verification read operation may be carried out using a program verification voltage. If threshold voltages of memory cells to be programmed don't reach the program verification voltage, a program voltage increased by a desired (or alternatively predetermined) voltage may be applied to the selected word line. The ISPP operation may be carried out by iterating a program voltage applying operations and a verification read operation.

There is restricted the number of loops where an ISPP voltage is applied to a selected word line. If memory cells (i.e., bad memory cells) not reaching the program verification voltage within the restricted loop number exist, the control logic 150 generates a fail signal FS indicating program fail. The fail signal FS is sent to the controller 200.

According to example embodiments, the ISPP manner can be applied to an erase operation. In this case, a selected memory block is supplied with an erase voltage which is increased stepwise. After the erase voltage is applied to the selected memory block, a verification read operation is carried out using an erase verification voltage. Like the program operation using the ISPP manner, an erase voltage applying operation and a verification read operation are iterated. For example, the control logic 150 performs the verification read operation in which pages within the erased/selected memory block are sequentially read. The control logic 150 sequentially generates page addresses of the erased memory block at the verification read operation.

According to example embodiments, there is restricted the number of loops where ISPP voltages are applied to the selected memory block.

If memory cells (i.e., bad memory cells) not reaching the erase verification voltage within the restricted loop number

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exist, the control logic 150 generates a fail address FAD indicating an address of an erase-failed page.

According to example embodiments, the erase operation may be accomplished by applying an erase voltage to the selected memory block once. After the erase voltage is applied to the selected memory block, a verification read operation is performed using an erase verification voltage. If memory cells (i.e., bad memory cells) not reaching the erase verification voltage exist, the control logic 150 generates an address of an erase-failed page as a fail address FAD.

FIG. 3 is a diagram illustrating a memory cell array in FIG. 2. Referring to FIG. 3, a memory cell array 110 includes a plurality of memory blocks BLK1 to BLKz. Each of the memory blocks BLK1 to BLKz is formed to have a three-dimensional structure (or, a vertical structure). For example, each of the memory blocks BLK1 to BLKz includes structures extending along first to third directions. For example, each of the memory blocks BLK1 to BLKz includes a plurality of NAND strings NS extending along the second direction. A plurality of NAND strings NS is provided to be arranged along the first and third directions.

Each of the memory blocks BLK1 to BLKz is connected with a plurality of bit lines BL, a plurality of string selection lines SSL, a plurality of ground selection lines GSL, a plurality of word lines WL, and a common source line CSL. The memory blocks BLK1 to BLKz will be more fully described with reference to FIG. 4.

According to example embodiments, the memory blocks BLK1 to BLKz may be selected by an address decoder 120 in FIG. 2. For example, the address decoder 120 is configured to select a memory block BLKi (i=1 to k) corresponding to a decoded block address among the memory blocks BLK1 to BLKz.

FIG. 4 is a perspective view of one of memory blocks in FIG. 3. FIG. 5 is a cross-sectional view taken along a line V-V' in FIG. 4.

A memory block includes a substrate 111. The substrate 111 may be a well having a first conductive type, for example. The substrate 111 may be a p-well in which the Group III element such as boron is injected, but example embodiments are not limited thereto. The substrate 111 may be a pocket p-well which is provided within an n-well. Below, it is assumed that the substrate 111 is a p-well (or, a pocket p-well). However, the substrate 111 is not limited to a p-type.

A plurality of doping regions 311 to 313 extend along the first direction in the substrate 111. The doping regions 311 to 313 are spaced apart from one another along the third direction. The doping regions 311 to 313 illustrated in FIGS. 4 to 6 are defined as a first doping region 311, a second doping region 312, and a third doping region 313.

The first to third doping regions 311 to 313 have a second conductive type different from that of the substrate 111. For example, the first to third doping regions 311 to 313 are an n-type. Below, it is assumed that the first to third doping regions 311 to 313 are the n-type. However, the first to third doping regions 311 to 313 are not limited to the n-type.

Between two adjacent doping regions of the first to third doping regions 311 to 313, a plurality of insulation materials 112 and 112a are provided sequentially on the substrate 111 along the second direction (i.e., a direction perpendicular to the substrate 111). The insulation materials 112 and 112a are spaced apart along the second direction. The insulation materials 112 and 112a extend along the first direction. For example, the insulation materials 112 and 112a may include an insulation material such as a dielectric material, for example a silicon oxide film, but example embodiments are

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not limited thereto. A thickness of the insulation material **112a** contacting with the substrate **111** is thinner than that of the insulation material **112**.

Between two adjacent doping regions of the first to third doping regions **311** to **313**, a plurality of semiconductor pillars **PL11**, **PL12**, **PL21**, and **PL22** are arranged sequentially along the first direction so as to penetrate the plurality of insulation materials **112** and **112a** along the second direction. For example, the semiconductor pillars **PL11**, **PL12**, **PL21**, and **PL22** may contact with the substrate **111** through the insulation materials **112** and **112a**.

The semiconductor pillars **PL11**, **PL12**, **PL21**, and **PL22** may be formed of multiple layers, respectively. Each of the semiconductor pillars **PL11**, **PL12**, **PL21**, and **PL22** includes a channel film **114** and an inner material **115**. In the semiconductor pillars **PL11**, **PL12**, **PL21**, and **PL22**, an inner material and a channel film surrounding the inner material are provided.

The channel films **114** include a semiconductor material (e.g., silicon such as polycrystalline silicon, but not limited thereto) having a first conductive type. For example, the channel films **114** may include a semiconductor material (e.g., silicon) having the same conductive type as the substrate **111**. Below, it is assumed that the channel films **114** include p-type silicon. However, the channel films **114** are not limited to the p-type silicon. For example, the channel films **114** can include an intrinsic semiconductor being a nonconductor.

The inner materials **115** may include an insulation material. For example, the inner materials **115** may include an insulation material such as a dielectric material, for example silicon oxide, but example embodiments are not limited thereto. Alternatively, the inner materials **115** may include air gap.

Between two adjacent doping regions of the first to third doping regions **311** to **313**, information storage films **116** are on exposed surfaces of the insulation materials **112** and **112a** and the semiconductor pillars **PL11**, **PL12**, **PL21**, and **PL22**. In FIG. 4, for example, a thickness of each of the information storage films **116** is less than a distance between the insulation materials **112** and **112a**. The closer to the substrate, the narrower a width of each of the semiconductor pillars **PL11**, **PL12**, **PL21**, and **PL22**.

Between two adjacent doping regions of the first to third doping regions **311** to **313**, conductive materials **CM1** to **CM8** are on exposed surfaces of the information storage films **116**. In particular, the conductive materials **CM1** to **CM8** extending along the first direction are provided between an information storage film provided at a lower surface of an upper insulation material of the insulation materials **112** and **112a** and an information storage film provided at an upper surface of a lower insulation material of the insulation materials **112** and **112a**. The conductive materials **CM1** to **CM8** may include a metallic conductive material, or a nonmetallic conductive material such as polysilicon (e.g., doped polysilicon), but example embodiments are not limited thereto.

An information storage film **116** on an upper surface of an insulation material **112** at the uppermost layer among the insulation materials **112** and **112a** can be removed. An information storage film **116** at a side opposite to the semiconductor pillars **PL11**, **PL12**, **PL21**, and **PL22** among the insulation materials **112** and **112a** can be removed.

A plurality of drains **320** are on the plurality of semiconductor pillars **PL11**, **PL12**, **PL21**, and **PL22**, respectively. The drains **320** may include a semiconductor material (e.g., silicon, such as doped polysilicon, but not limited thereto) having the second conductive type, for example. The drains **320** may include an n-type semiconductor material (e.g., silicon).

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Below, it is assumed that the drains **320** include n-type silicon. However, example embodiments are not limited thereto. The drains **320** can be extended to the upside of the channel films **114** of the semiconductor pillars **PL11**, **PL12**, **PL21**, and **PL22**.

Bit lines **BL1** and **BL2** extending in the third direction are on the drains **320** so as to be spaced apart from one another along the first direction. The bit lines **BL1** and **BL2** are coupled with the drains **320**. According to example embodiments, the drains **320** and the bit lines **BL1** and **BL2** may be connected via contact plugs (not shown). The bit lines **BL1** and **BL2** may include a metallic conductive material, or a nonmetallic conductive material such as polysilicon (e.g., doped polysilicon), but example embodiments are not limited thereto.

Memory block **BLK1** includes rows and columns of the semiconductor pillars **PL11**, **PL12**, **PL21**, and **PL22** (see FIG. 7). Semiconductor pillars **PL11** and **PL12** coupled with conductive materials **CM1** to **CM8** between the first doping region **311** and the second doping region **312** via the information storage films **115** are a first row of semiconductor pillars. Semiconductor pillars **PL21** and **PL22** coupled with conductive materials **CM1** to **CM8** between the second doping region **312** and the third doping region **313** via the information storage films **115** are a second row of semiconductor pillars. That is, a row direction is the first direction. Columns of semiconductor pillars **PL11**, **PL12**, **PL21**, and **PL22** are connected to the bit lines **BL1** and **BL2**. Semiconductor pillars **PL11** and **PL21** connected with the bit line **BL1** via the drains **320** are a first column of semiconductor pillars. Semiconductor pillars **PL12** and **PL22** connected with the bit line **BL2** via the drains **320** are a second column of semiconductor pillars. That is, a column direction is the third direction.

The conductive materials **CM1** to **CM8** have first to eighth heights, respectively, according to a distance from the substrate **111**. The conductive material **CM1** closest to the substrate **111** has the first height, and the conductive material **CM8** closest to the bit lines **BL1** and **BL2** has the eighth height.

Each of the semiconductor pillars **PL11**, **PL12**, **PL21**, and **PL22** constitutes a cell string with an adjacent information storage film **116** and an adjacent conductive material **CMj** ($j=1$ to 8). That is, the semiconductor pillars **PL11**, **PL12**, **PL21**, and **PL22** form cell strings with information storage films **116** and the conductive materials **CM1** to **CM8**.

Each cell string includes a plurality of cell transistors **CT** stacked in a direction perpendicular to the substrate. One **CT** of the plurality of cell transistors is illustrated in FIG. 6. The cell transistor **CT** will be more fully described with reference to FIG. 6.

FIG. 6 is a diagram illustrating one of cell transistors in FIG. 5. For example, a cell transistor having a fifth height among a plurality of cell transistors corresponding to a semiconductor pillar **PL11** arranged in a first row and a first column is illustrated.

Referring to FIGS. 4 to 6, a cell transistor is formed of a fifth conductive material **CMS**, a portion of a semiconductor pillar **PL11** adjacent to the fifth conductive material **CMS**, and an information storage film **116** provided between the conductive material **CMS** and the semiconductor pillar **PL11**.

The information storage films **116** extend to upper surfaces and lower surfaces of conductive materials **CM1** to **CM8** from regions between the conductive materials **CM1** to **CM8** and the semiconductor pillars **PL11**, **PL12**, **PL21**, and **PL22**. Each of the information storage films **116** includes first to third sub insulation films **117**, **118**, and **119**.

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In the cell transistors CT, the channel films 114 of the semiconductor pillars PL11, PL12, PL21, and PL22 may include the same p-type silicon as the substrate 111. The channel films 114 are formed in a direction perpendicular to the substrate 111. Accordingly, the channel films 114 of the semiconductor pillars PL11, PL12, PL21, and PL22 may act as a vertical body. Channels formed at the channel films 114 of the semiconductor pillars PL11, PL12, PL21, and PL22 are vertical channels.

The plurality of conductive materials CM1 to CM8 may act as a gate (or, a control gate).

The first sub insulation films 117 adjacent to the semiconductor pillars PL11, PL12, PL21, and PL22 may act as a tunneling insulation film. For example, the first sub insulation films 117 adjacent to the semiconductor pillars PL11, PL12, PL21, and PL22 may include a nitride film or a metal oxide film (e.g., an aluminum oxide film, a hafnium oxide film, etc.) or a silicon nitride film, but example embodiments are not limited thereto.

The second sub insulation films 118 may act as a charge storage film. For example, the second sub insulation films 118 may act as a charge trap film. For example, the second sub insulation films 118 may include a nitride film or a metal oxide film (e.g., an aluminum oxide film, a hafnium oxide film, etc.) or a silicon nitride film, but example embodiments are not limited thereto.

The third sub insulation films 119 adjacent to the conductive materials CM1 to CM8 may act as a blocking insulation film. According to example embodiments, the third sub insulation films 119 may be formed of a single layer or multiple layers. The third sub insulation films 119 may be a high dielectric film (e.g., an aluminum oxide film, a hafnium oxide film, etc., but example embodiments are not limited thereto) having a dielectric constant larger than the first and second sub insulation films 117 and 118. The third sub insulation films 119 may include a silicon oxide film.

According to example embodiments, the first to third sub insulation films 117 to 119 may include ONO (oxide-nitride-oxide).

The plurality of conductive materials CM1 to CM8 acting as a gate (or, a control gate), the third sub insulation films 119 acting as a block insulation film, the second sub insulation films 118 acting as a charge storage film, the first sub insulation films 117 acting as a tunneling insulation film, and the channel films 114 acting as a vertical body may operate as cell transistors CT. For example, the cell transistors CT may be a charge trap type cell transistor.

The cell transistors CT can be used for different purposes according to height. For example, among the cell transistors CT, at least one cell transistor placed at the uppermost is used as a string selection transistor SST. At least one cell transistor placed at the lowermost is used as a ground selection transistor GST. The remaining cell transistors are used as a memory cell.

The memory block BLK1 includes a plurality of sub-memory blocks. Each sub-memory block includes a plurality of memory layers. Each memory layer is formed of memory cells having the same height. Memory cells disposed at each of the second height to the seventh height form a memory layer. Each memory layer is formed of memory cells sharing a word line.

The conductive materials CM1 to CM8 extend along a row direction (or, the first direction) and are connected with the plurality of semiconductor pillars PL11, PL12, PL21, and PL22. That is, the conductive materials CM1 to CM8 constitute conductive lines interconnecting cell transistors CT of the semiconductor pillars (PL11 and PL12) or (PL21 and PL22) in the same row.

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According to example embodiments, the conductive materials CM1 to CM8 may be used as a string selection line SSL, a ground selection line GSL, or a word line WL according to the height.

FIG. 7 is a circuit diagram illustrating an equivalent circuit of a memory block. Referring to FIGS. 4 to 7, cell strings CS11 and CS21 are between a first bit line BL1 and a common source line CSL, and cell strings CS12 and CS22 are provided between a second bit line BL2 and the common source line CSL. The cell strings CS11, CS21, CS12, and CS22 correspond to semiconductor pillars PL11, PL21, PL12, and PL22, respectively.

The semiconductor pillar PL11 in a first row and a first column forms the cell string CS11 in the first row and the first column together with conductive materials CM1 to CM6 and information storage films 116. The semiconductor pillar PL12 in a first row and a second column forms the cell string CS12 in the first row and the second column together with the conductive materials CM1 to CM6 and the information storage films 116. The semiconductor pillar PL21 in a second row and the first column forms the cell string CS21 in the second row and the first column together with the conductive materials CM1 to CM6 and the information storage films 116. The semiconductor pillar PL22 in the second row and the second column forms the cell string CS22 in the second row and the second column together with the conductive materials CM1 to CM6 and the information storage films 116.

In the cell strings CS11, CS21, CS12, and CS22, cell transistors of the first height may act as a ground selection transistor GST. For example, the first conductive materials CM1 are interconnected to form a ground selection line GSL.

In the cell strings CS11, CS21, CS12, and CS22, cell transistors of the eighth height may act as a string selection transistor SST. The string selection transistors SST are connected with first and second string selection lines SSL1 and SSL2. Cell strings in the same row share a string selection line. Cell strings in different rows are connected with different string selection lines, respectively. The first and second string selection lines SSL1 and SSL2 correspond to the eighth conductive materials CM8, respectively. That is, it is understood that the semiconductor pillars PL11, PL12, PL21, and PL22, that is, rows of the cell strings CS11, CS12, CS21, and CS22 are defined by the first and second string selection lines SSL1 and SSL2.

In the cell strings CS11, CS21, CS12, and CS22, cell transistors of each of the second to seventh heights constitute a memory layer. That is, memory cells having the same height constitute a memory layer (refer to FIG. 9). Memory cells of each memory layer may share a word line. For example, cell transistors of the second to seventh heights may constitute first to sixth memory layers.

A first word line WL1 is formed by connecting the second conductive materials CM2 in common. A second word line WL2 is formed by connecting the third conductive materials CM3 in common. A third word line WL3 is formed by connecting the fourth conductive materials CM4 in common. A fourth word line WL4 is formed by connecting the fifth conductive materials CM5 in common. A fifth word line WL5 is formed by connecting the sixth conductive materials CM6 in common. A sixth word line WL6 is formed by connecting the seventh conductive materials CM7 in common.

The common source line CSL is connected in common with the cell strings CS11, CS12, CS21, and CS22. For example, the common source line CSL is formed by connecting the first to third doping regions 311 to 313.

As described above, the string selection lines SSL1 and SSL2, the word lines WL1 to WL6, and the ground selection

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line GSL of a selected memory block are connected with the address decoder 120. The address decoder 120 selects the string selection lines SSL1 and SSL2, the word lines WL1 to WL6, and the ground selection line GSL of the selected memory block.

Memory cells of the same height are connected in common with a word line. Accordingly, when a word line of a specific height is selected, all cell strings CS11, CS12, CS21, and CS22 connected with the selected word line are selected.

Cell strings of different rows are connected with different string selection lines, respectively. Accordingly, cell strings (CS11 and CS12) or (CS21 and CS22) of an unselected row among cell strings CS11, CS12, CS21, and CS22 connected with the same word line are electrically separated from the bit lines BL1 and BL2 by selecting and unselecting the first and second string selection lines SSL1 and SSL2. Cell strings (CS21 and CS22) or (CS11 and CS12) of a selected row are electrically connected with the bit lines BL1 and BL2.

That is, rows of the cell strings CS11, CS12, CS21, and CS22 are selected by selecting and unselecting the first and second string selection lines SSL1 and SSL2. Columns of cell strings in the selected row are selected by selecting the bit lines BL1 and BL2.

A program operation and a read operation may be carried out by the page. That is, in cell strings connected with the same string selection line, memory cells connected with the same word line are programmed at the same time. Further, in cell strings connected with the same string selection line, memory cells connected with the same word line are read at the same time. At a program operation and a read operation, an address ADDR transferred to a nonvolatile memory portion 100 from a controller 200 may correspond to a specific page.

An erase operation may be performed by the memory block. Memory cells included in a memory block are erased at the same time. At erasing, an address ADDR transferred to a nonvolatile memory portion 100 from a controller 200 may correspond to a memory block.

String selection lines SSL1 and SSL2, word lines WL1 to WL6, and a ground selection line GSL of unselected memory blocks are electrically separated from the address decoder 120 by pass circuits of a block gating part corresponding to the unselected memory blocks. Ground circuits of the block gating part corresponding to the unselected memory blocks may supply a low voltage (e.g., a ground voltage) to the string selection lines SSL1 and SSL2 and the ground selection line GSL of the unselected memory blocks. Accordingly, when string selection transistors SST and ground selection transistors GST of the unselected memory blocks are turned off, the unselected memory blocks are electrically separated from the bit lines BL1 and BL2 and the common source line CSL.

The closer to the substrate 111, the narrower widths of the semiconductor pillars PL11, PL12, PL21, and PL22. A first width P1 (refer to FIG. 5) of the semiconductor pillar PL21 corresponds to a fifth height. A second width P2 (refer to FIG. 5) adjacent to the substrate 111 corresponds to a fourth height. The second width P2 is narrower than the first width P1.

An area of a channel of a memory cell adjacent to the substrate 111 is less in size than that of a memory cell far away from the substrate 111. When F-N tunneling is caused due to a program voltage, the amount of a current flowing between a word line and a channel increases in proportion to a decrease in an area of a channel of a memory cell. The means that an increasing speed of a threshold voltage of a memory cell increases in proportion to a decrease in an area of a channel of a memory cell. Accordingly, it is difficult to control a threshold voltage of a memory cell as its channel area decreases.

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That is, the reliability of data stored in a memory cell is lowered when its channel area decreases.

According to an example embodiments of inventive concepts, if a bad memory cell is detected, a memory layer including the detected bad memory cell is treated as a bad area. At least one of memory layers between the memory layer including the bad memory cell and the substrate 111 is treated as a bad area.

It is assumed that at least one of memory cells of a fifth height is a bad memory cell. According to example embodiments, memory cells of a fourth height are treated as a bad area with the memory cells of the fifth height. Memory cells of second to fourth heights can be treated as a bad area with the memory cells of the fifth height.

In FIGS. 4 to 7, the memory block BLK1 is assumed to have the first height to the eighth height and to include 2×2 cell strings. However, the number of cell strings disposed in a column direction may be proportional to a height of the memory block BLK1.

According to example embodiments, if the memory block BLK1 has the first to eighth heights, it may include 1×8 cell strings. At this time, the memory block BLK1 may be connected with eight string selection lines and a ground selection line.

If the memory block BLK1 has the first to eighth heights, it may include 1×16 cell strings. At this time, the memory block BLK1 may be connected with 16 string selection lines and a ground selection line.

FIG. 8 is a flowchart illustrating a bad area managing method of a nonvolatile memory device in FIG. 1. Referring to FIGS. 1 and 8, in operation S110, a controller 200 accesses a selected memory block by sending an address ADDR. At a program/read operation, the address ADDR may correspond to a selected page of the selected memory block. At an erase operation, the address ADDR may correspond to the selected memory block.

In operation S120, the controller 200 judges whether a bad memory cell is detected. The controller 200 may judge whether a bad memory cell is detected, according to a fail signal FS and a fail address FAD. If a bad memory cell is detected, the method proceeds to operation S130.

In operation S130, the controller 130 treats at least one memory layer of the accessed memory block as a bad area. At this time, a memory layer treated as a bad area may include the bad memory cell.

According to example embodiments of inventive concepts, a part of the accessed memory block is treated as a bad area. This means that the accessed memory block is not treated as a bad area. Accordingly, it is possible to reduce the number of memory cells treated as a bad area.

It is assumed that a first memory cell and a second memory cell are included in different memory layers, respectively. Diameters of semiconductor pillars corresponding to memory layers are different from one another. Accordingly, threshold voltages and reliabilities of the first and second memory cells may differentiate. In this case, memory layers having the reliability higher than that of a memory layer including a bad memory cell, that is, memory layers far away from a substrate 111 as compared with the memory layer including a bad memory cell are not treated as a bad area. This means that a lifetime of memory layers not treated as a bad area increases.

FIG. 9 is a diagram conceptually illustrating memory cells of a memory block. Referring to FIGS. 4 and 9, a memory block BLK1 includes a first memory layer L1 to a sixth memory layer L6. The first to sixth memory layers are

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sequentially stacked in a second direction (i.e., a direction perpendicular to a substrate **111**).

Below, it is assumed that the memory block **BLK1** is connected with N string selection lines, M bit lines, and one ground selection line. According to this assumption, N memory cells are arranged in a third direction, and M memory cells are arranged in a first direction.

The first to sixth memory layers **L1** to **L6** are connected with first to sixth word lines **WL1** to **WL6**, respectively. That is, memory cells included in each memory layer share a word line.

It is assumed that a memory cell **MC1** (represented by a hatched square box) is a bad memory cell. A nonvolatile memory portion **100** (refer to FIG. 1) generates a fail signal **FS** when a program operation is carried out with respect to a page including the memory cell **MC1** of the fourth memory layer **L4**. The controller **200** treats the fourth memory layer **L4** as a bad area in response to the fail signal **FS**. According to example embodiments, when data stored in the memory block **BLK1** is erased, the nonvolatile memory portion **100** generates a fail address **FAD** corresponding to a page including the memory cell **MC1**. The controller **200** treats the fourth memory layer **L4** as a bad area in response to the fail address **FAD**.

FIG. 10 is a diagram illustrating an address management register in FIG. 1. In FIG. 10, there is illustrated bad area information after pages included in a fourth memory layer **L4** of a memory block **BLK1** in FIG. 9 are treated as a bad area.

Pages included in the fourth memory layer **L4** are not used. That is, a flash translation layer **210** does not generate physical addresses corresponding to the pages in the fourth memory layer **L4**. In the memory block **BLK1**, pages of remaining memory layers other than the fourth memory layer **L4** are used.

FIG. 11 is a flowchart illustrating a bad area managing method according to example embodiments of inventive concepts. Referring to FIGS. 1 and 10, in operation **S210**, a controller **200** accesses a selected memory block by sending an address **ADDR** to a nonvolatile memory portion **100**. In operation **S220**, the controller **200** judges whether a bad memory cell is detected. The controller **200** judges whether a bad memory cell is detected, according to a fail signal **FS** and a fail address **FAD**. If a bad memory cell is detected, the method proceeds to operation **S230**.

In operation **S230**, an address management circuit **211** (refer to FIG. 1) judges whether one or more memory layers exist between a substrate **111** and a memory layer including a bad memory cell. If at least one memory layer exists between the substrate **111** and the memory layer including a bad memory cell, the method proceeds to operation **S240**. If no memory layer exists between the substrate **111** and the memory layer including a bad memory cell, the method proceeds to operation **S250**.

In operation **S240**, the address management circuit **211** treats both the memory layer including a bad memory cell and the at least one memory layer between the substrate **111** and the memory layer including a bad memory cell, as a bad area.

As described in FIGS. 4 to 7, a plurality of semiconductor pillars include channels of memory cells of a memory block **BLK1**. The closer to a substrate **111**, the narrower widths of the semiconductor pillars. Among memory cells connected with the same semiconductor pillar, a channel area of a memory cell adjacent to the substrate **111** is less in size than that far away from the substrate **111**. As a channel area of a memory cell decreases, the reliability of program, read, and erase operations may be lowered. The reliability of data stored in a memory layer adjacent to the substrate **111** may

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become stochastically lower as compared with that of data stored in a memory layer far away from the substrate **111**. According to an exemplary embodiment of the inventive concept, at least one memory layer between the substrate **111** and a memory layer including a bad memory cell may be treated as a bad area with the memory layer including a bad memory cell.

In operation **S250**, the address management circuit **211** treats the memory layer including a bad memory cell as a bad area.

FIG. 12 is a diagram for describing the case that third and fourth memory layers are treated as a bad area. In FIG. 12, there are conceptually illustrated memory cells of a memory block.

It is assumed that a memory cell **MC1** (represented by a hatched square box) is a bad memory cell. If a bad memory cell is detected, an address management circuit **211** may treat a fourth layer **L4** including the memory cell **MC1** and at least one memory layer **L3** between the fourth memory layer **L4** and a substrate **111** as a bad area.

FIG. 13 is a diagram for describing the case that first to fourth memory layers are treated as a bad area. An address management circuit **211** may treat a fourth layer **L4** including the memory cell **MC1** and all memory layers **L1** to **L3** between the fourth memory layer **L4** and a substrate **111** as a bad area.

FIG. 14 is a diagram for describing the case that second sub-memory layer is treated as a bad area.

A plurality of memory layers **L1** to **L6** are divided into a plurality of sub-memory blocks **SBLK1** to **SBLK3**. That is, each sub-memory block may include at least one memory layer.

According to example embodiments of inventive concepts, an address management circuit **211** manages a bad area by a unit of a sub-memory block. The address management circuit **211** may treat a sub-memory block **SBLK2** including a bad memory cell as a bad area.

FIG. 15 is a diagram for describing the case that first and second sub-memory layers are treated as a bad area.

According to example embodiments of inventive concepts, at least one sub-memory block **SBLK1** between a substrate **111** and a second sub-memory block **SBLK2** including a bad memory cell **MC1** is treated as a bad area with the second sub-memory block **SBLK2** including the bad memory cell **MC1**. Alternatively, all sub-memory blocks between the substrate **111** and the second sub-memory block **SBLK2** can be treated as a bad area with the second sub-memory block **SBLK2** including the bad memory cell **MC1**.

FIG. 16 is a perspective view illustrating a memory block in FIG. 3 according to example embodiments of inventive concepts. FIG. 17 is a cross-sectional view of a memory block taken along a line XVII-XVII'. As compared with a memory block **BLK1** described with reference to FIGS. 4 to 6, each semiconductor pillar **PL** of a memory block in FIG. 16 includes a first sub semiconductor pillar **PLa** and a second sub semiconductor pillar **PLb**. Duplicate description about the same elements is thus omitted.

Referring to FIGS. 16 and 17, the first sub semiconductor pillar **PLa** is provided on a substrate **111**. For example, a channel film **114a** of the first sub semiconductor pillar **PLa** may include a p-type silicon material. The channel film **114a** of the first sub semiconductor pillar **PLa** may act as a body of a second direction. An inner material **115a** of the first sub semiconductor pillar **PLa** is formed of an insulation material.

A second sub semiconductor pillar **PLb** is provided on the first sub semiconductor pillar **PLa**. For example, a channel film **114b** of the second sub semiconductor pillar **PLb** may

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include a p-type silicon material. The channel film **114b** of the second sub semiconductor pillar PLb may act as a body of the second direction. An inner material **115b** of the second sub semiconductor pillar PLb is formed of an insulation material. The closer to the substrate **111**, the narrower widths of the first and second sub semiconductor pillars PLa and PLb.

The channel film **114a** of the first sub semiconductor pillar PLa is connected with the channel film **114b** of the second sub semiconductor pillar PLb. For example, the channel film **114a** of the first sub semiconductor pillar PLa is connected with the channel film **114b** of the second sub semiconductor pillar PLb via a p-type silicon pad (not shown).

The first sub semiconductor pillar PLa may provide a channel to cell transistors of the first to fourth heights. The second sub semiconductor pillar PLb may provide a channel to cell transistors of the fifth to eighth heights. An equivalent circuit of the memory block BLK1 described with reference to FIGS. **16** and **17** may be configured the same as that in FIG. **7**. Cell transistors of the second to fourth heights may act as a memory cell, and cell transistors of the fifth to seventh heights may act as a memory cell. Memory cells of each height are connected with one word line. Memory cells connected with one word line may constitute a memory layer.

Below, it is assumed that the memory block BLK1 is connected with N string selection lines and M bit lines. With this assumption, N memory cells are disposed in a third direction, and M memory cells are disposed in a first direction.

FIG. **18** is a diagram conceptually illustrating memory cells of a memory block in FIGS. **16** and **17**. In FIG. **18**, it is assumed that a memory cell MC2 (represented by a hatched square box) is a bad memory cell.

Referring to FIGS. **16** to **18**, the memory cell MC2 is included in a sixth memory layer L6. An address management circuit **211** may treat the sixth memory layer L6 as a bad area. The address management circuit **211** may treat at least one of other memory layers sharing a sub semiconductor pillar with the sixth memory layer L6 as a bad area.

FIG. **19** is a block diagram illustrating a nonvolatile memory portion according to example embodiments of inventive concepts. Referring to FIG. **19**, a nonvolatile memory portion **2000** includes a memory cell array **110**, an address decoder **120**, a read/write circuit **130**, a data input/output circuit **140**, and control logic **2500**. The nonvolatile memory portion **2000** in FIG. **19** is substantially identical to that in FIG. **2** except for the control logic **2500**, and duplicative description thereof is thus omitted.

The control logic **2500** includes a bad area management register **2510**. The bad area management register **2510** includes bad area information. At erasing, programming, and reading, the control logic **2500** controls the address decoder **120** according to the bad area information such that a specific voltage is applied to word lines connected with a bad area.

The control logic **2500** may temporarily store an address ADDR input from a controller **200**. The control logic **2500** updates the bad area information stored in the bad area management register **2510** when program fail or read fail is caused. Bad area information stored in the bad area management register **2510** may be received from the controller **200**.

FIG. **20** is a diagram illustrating a threshold voltage distribution of memory cells in a memory cell array in FIG. **19**. For convenience of explanation, FIG. **20** illustrates an example of a threshold voltage distribution formed in the event that 1-bit data is stored in each memory cell of a memory cell array **110**. In FIG. **20**, a horizontal axis indicates a threshold voltage, and a vertical axis indicates the number of memory cells.

Referring to FIGS. **19** and **20**, normally programmed memory cells may have a threshold voltage corresponding to

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an erase state E or a program state P. At a read operation, a first voltage V1 is applied to unselected word lines. The first voltage V1 is higher in level than threshold voltages corresponding to the erase and program states E and P. Accordingly, memory cells connected with the unselected word lines are turned on. A second voltage V2 is applied to a selected word line. Data of a selected page may be read by judging whether memory cells connected with the selected word line have the erase state E or the program state P, based upon the second voltage V2.

Threshold voltages of memory cells can be varied due to interference between memory cells. For example, threshold voltages of memory cells having the program state P can be varied to threshold voltages corresponding to a first state S1.

Some of memory cells having the first state S1 may have a threshold voltage lower in level than the first voltage V1. The remaining of the memory cells having the first state S1 may have a threshold voltage higher in level than the first voltage V1. If there are selected word lines connected with memory cells having a threshold voltage higher in level than the first voltage V1, read data may include erroneous bits. The erroneous bits may be detected and corrected by an error correcting block **220** in FIG. **1**.

If the number of memory cells, having a threshold voltage higher in level than the first voltage V1, among memory cells of a selected word line exceeds a correctable erroneous bit number, the error correcting block **220** may generate a read fail signal RF. Memory layers or sub-memory blocks including the memory cells of the selected word line are judged to be a bad area. Information about the bad area thus judged is sent to a flash translation layer **210**.

As programming using an ISPP manner is failed, the control logic **2500** generates the fail signal FS and simultaneously stores information about the selected page in the bad area management register **2510**.

As erasing using an ISPE (incremental step pulse erasing) manner is failed, the control logic **2500** generates the fail address FAD and simultaneously stores the fail address FAD in the bad area management register **2510**.

At a read operation, the control logic **2500** controls the address decoder **120** according to the bad area information such that a third voltage V3 is applied to word lines connected with the bad area. That is, the first voltage V1 is applied to unselected word lines, the second voltage V2 is applied to a selected word line, and the third voltage V3 higher in level than the first voltage V1 is applied to word lines connected with the bad area.

Likewise, at a program operation, the control logic **2500** controls the address decoder **120** such that a voltage higher in level than a voltage applied to unselected word lines is applied to word lines connected with the bad area.

Likewise, at an erase operation, the control logic **2500** controls the address decoder **120** such that a voltage higher in level than an erase voltage applied to unselected memory cells is applied to memory cells of the bad area.

According to example embodiments, after erasing data stored in a memory block including the bad area, a desired (or alternatively predetermined) voltage (e.g., the second voltage V2) may be applied to word lines connected with the bad area. In particular, the controller **200** controls the nonvolatile memory portion **2000** such that data stored in a memory block including the bad area is stored in another memory block. The controller **200** control the nonvolatile memory portion **2000** such that data stored in a memory block including the bad area is erased. Erased memory cells may have the erase state E.

At erasing, programming, or reading, the control logic **2500** may discriminate word lines connected with the bad

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area, based upon the bad area information stored in the bad area management register **2510**. Under the control of the control logic **2500**, a specific voltage (e.g., the second voltage **V2**) may be applied to word lines connected with the bad area such that memory cells included in the bad area are turned on.

According to example embodiments, the control logic may control the address decoder **120** such that the first voltage **V1** is applied to word lines connected with the bad area like the unselected word lines.

A threshold voltage of a program-failed memory cell may be lower in level than a threshold voltage corresponding to the program state **P**. A threshold voltage of an erase-failed memory cell (a bad memory cell) may be lower in level than a threshold voltage corresponding to the program state **P**. It is assumed that bad memory cells have a threshold voltage corresponding to the second state **S2**. In this case, although the first voltage **V1** applied to unselected word lines is applied to word lines connected with the bad area at a read operation, the bad memory cells are turned on. Accordingly, at a read operation, voltages of word lines connected with the bad area are controlled to be identical to those applied to unselected word lines.

The control logic **2500** may treat word lines connected with the bad area like word lines connected with a normal area, without considering the bad area. In this case, the bad area management register **2510** storing the bad area information is not needed.

At a program operation, the control logic **2500** may treat word lines connected with the bad area like word lines connected with a normal area, without considering the bad area. A program voltage applied to the word lines connected with the bad area may be identical to program voltages applied to unselected word lines.

At an erase operation, the control logic **2500** may treat word lines connected with the bad area like word lines connected with a normal area, without considering the bad area. An erase voltage applied to the word lines connected with the bad area may be identical to program voltages applied to unselected word lines.

FIG. **21** is a diagram for describing a mapping relationship between physical addresses and logical addresses according to example embodiments of inventive concepts. Referring to FIG. **21**, a controller **200** may receive a first sector **SECO** to a *j*th sector **SECj** as a logical address **LA** from a host. Below, FIG. **21** is described under the assumption that a memory block **BLK1** includes a sub-memory block judged to be a bad area.

According to example embodiments of inventive concepts, in the memory block **BLK1**, an address management circuit **211** converts a logical address **LA** to generate a physical address **PA** by a unit of a sub-memory block. This is referred to as sub block mapping. The address management circuit **211** does not generate a physical address **PA** corresponding to a sub-memory block of the memory block **BLK1** judged to be a bad area. Remaining memory blocks of the memory block **BLK1** other than the bad area may be used.

In case of memory blocks **BLK2** to **BLKz** not including a bad area, the address management circuit **211** performs block mapping. That is, the address management circuit **211** provides a physical address **PA** by a sub-memory block unit when a memory block including a bad area is selected. The address management circuit **211** provides a physical address **PA** by a memory block unit when a memory block not including a bad area is selected.

FIG. **22** is a diagram for describing a method of storing data in a first memory block including a bad area according to a mapping relationship described in FIG. **21**. It is assumed that

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a controller **200** sequentially receives data for first programming (①) and data for second programming (②) from a host. Further, it is assumed that a third sub-memory block **SBLK3** of a first memory block **BLK1** is a bad area.

Referring to FIGS. **1**, **21**, and **22**, the controller **200** may receive a logical address **LA** from the host together with the data for the first programming (①). An address management circuit **211** may generate physical addresses **PA** corresponding to sub-memory blocks **SBLK1**, **SBLK2**, and **SBLK4** to **SBLKq** of the first memory block **BLK1** and a second memory block **BLK2**, based upon the logical address **LA**. The address management circuit **211** further generates offset information being information about addresses of pages to be programmed in the second memory block **BLK2**. According to the physical addresses **PA**, a program operation may be performed with respect to remaining sub-memory blocks **SBLK1**, **SBLK2**, and **SBLK4** to **SBLKq** of the first memory block **BLK1** other than the third sub-memory block **SBLK3** and the second memory block **BLK2**. The address management circuit **211** stores the logical address **LA**, the physical address **PA**, and the mapping relationship between the logical address **LA** and the physical address **PA** in an address management register **212**. Further, the logical address **LA**, the physical address **PA**, and the mapping relationship between the logical address **LA** and the physical address **PA** may be stored in a nonvolatile memory portion **110**. That a physical address **PA** is stored in the address management register **212** means that data is previously stored in an area corresponding to the stored physical address **PA**.

The controller **200** receives data and a logical address **LA** for the second programming (②). The address management circuit **211** does not generate physical addresses **PA** corresponding to sub-memory blocks of the first memory block **BLK1** and the second memory block **BLK2**, based upon physical addresses **PA** stored in the address management register **212**.

The address management circuit **211** generates physical addresses **PA** corresponding to third and fourth memory blocks **BLK3** and **BLK4** based upon a logical address **LA**. The third and fourth memory blocks **BLK3** and **BLK4** are programmed according to the physical addresses **PA**. As understood from the description of FIG. **22**, a wasted area **WA** exists within memory blocks in which data is stored.

FIG. **23** is a diagram for describing a method according to example embodiments of storing data in a first memory block including a bad area according to a mapping relationship described in FIG. **21**. Referring to FIG. **23**, a first memory block **BLK1** including a bad area is used as a log memory block. The term "log memory block" is used to call a memory block in which data is partially stored. Alternatively, in the event that data in a first memory block is stored in a second memory block according to a copy-back operation, the term "log memory block" is used to call the first memory block.

It is assumed that an amount of data to be programmed is more than that of data capable of being stored in one memory block and less than that of data capable of being stored in two memory blocks. In this case, all memory cells of the second memory block **BLK2** are programmed, and a part of memory cells of the first memory block **BLK1** is programmed. At this time, the first memory block **BLK1** is called a log memory block.

Data for the first programming (①) and data for the second programming (②) are sequentially received from a host. It is assumed that an amount of data for each of the first programming and the second programming is more than that of data capable of being stored in one memory block and less than that of data capable of being stored in two memory blocks.

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According to example embodiments of inventive concepts, the first memory block BLK1 including a bad area is used as a log memory block. The data for the first programming (①) is stored in the whole second memory block BLK2 and a first sub-memory block SBLK1 of the first memory block BLK1. The data for the second programming (②) is stored in the whole third memory block BLK3 and a second sub-memory block SBLK2 of the first memory block BLK1. Accordingly, it is possible to reduce a wasted area WA which exists within memory blocks in which data is stored.

FIG. 24 is a diagram for describing a mapping relationship between physical addresses and logical addresses according to example embodiments of inventive concepts. It is assumed that a first memory block BLK1 includes a memory layer judged to be a bad area.

In the first memory block BLK1, an address management circuit 211 performs page mapping. At this time, the address management circuit 211 does not generate a physical address PA corresponding to a page judged to be a bad area. That is, the address management circuit 211 generates physical addresses PA corresponding to remaining pages of the first memory block BLK1 other than the bad area. In case of remaining memory blocks BLK2 to BLKz not including a bad area, the address management circuit 211 performs page mapping, sub block mapping, or block mapping. In FIG. 24, there is shown a mapping relationship between logical addresses and physical addresses when the block mapping is performed with respect to the memory blocks BLK2 to BLKz.

The address management circuit 211 provides a physical address PA by a page unit when a memory block including a bad area is selected. The address management circuit 211 provides a physical address PA by a memory block unit when a memory block not including a bad area is selected.

FIG. 25 is a block diagram illustrating an application of a nonvolatile memory device in FIG. 1.

Referring to FIG. 25, a nonvolatile memory device 3000 includes a nonvolatile memory portion 3100 and a controller 3200. The nonvolatile memory portion 3100 includes a plurality of nonvolatile memory chips. The plurality of nonvolatile memory chips may be classified into a plurality of groups. Nonvolatile memory chips in each group may communicate with the controller 3200 via a common channel.

Each nonvolatile memory chip is substantially identical to a nonvolatile memory portion 100 in FIG. 1. Each nonvolatile memory chip includes a plurality of memory blocks. Each memory block may include a plurality of memory layers stacked on a substrate 111. Each memory layer may include a plurality of memory cells arranged in a direction parallel with the substrate 111.

The controller 3200 operates the same as that described with reference to FIG. 1. That is, the controller 3200 includes an error correcting block 220 and a flash translation layer (FTL) 210 configured to translate a logical address into a physical address. The FTL 210 may be configured to manage a bad area of each nonvolatile memory chip by a memory layer unit or a sub-memory block unit. The controller 3200 provides addresses to nonvolatile memory chips according to a physical address provided by the FTL 210.

FIG. 25 illustrates the case where a plurality of nonvolatile memory chips are connected with one channel. However, the nonvolatile memory device 3000 can be modified such that one nonvolatile memory chip is connected with one channel.

FIG. 26 is a block diagram illustrating a computing system including a nonvolatile memory device in FIG. 25. Referring to FIG. 26, a computing system 4000 includes a CPU 4100, a

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RAM 4200, a user interface 4300, a power supply 4400, a system bus 4500, and a nonvolatile memory device 3000.

The nonvolatile memory device 3000 is electrically connected with the CPU 4100, the RAM 4200, the user interface 4300, and the power supply 4400 via the system bus 4500. Data provided via the user interface 4300 or processed by the CPU 4100 is stored in the nonvolatile memory device 3000.

FIG. 26 illustrates the case where a nonvolatile memory portion 3100 is connected with the system bus 4500 via a controller 3200. However, example embodiments are not limited thereto and the nonvolatile memory portion 3100 can be connected directly to the system bus 4500. In this case, a function of the controller 3200 may be executed by the CPU 4100. Further, the CPU 4100 may include a flash translation layer 210 described in FIG. 1.

In FIG. 26, the nonvolatile memory device 3000 described with reference to FIG. 25 can be replaced with a nonvolatile memory device 1000 described with reference to FIG. 1.

In this embodiment, the computing system 4000 may be configured to include all of nonvolatile memory devices 1000 and 3000 described in FIGS. 1 and 25.

According to example embodiments of inventive concepts, a controller 200 judges whether an accessed memory block includes a bad memory cell, based upon a fail signal FS or a fail address FAD. If a bad memory cell is detected, an address management circuit 211 updates bad area information stored in an address management register 212 such that at least one memory layer of the accessed memory block is treated as a bad area. At this time, the controller 200 stores the updated bad area information in a nonvolatile memory portion 100.

According to example embodiments, if a bad memory cell is detected, the address management circuit 211 updates bad area information stored in the address management register 212 such that at least one sub-memory block of the accessed memory block is treated as a bad area. It is possible to manage a bad area by the memory layer or the sub-memory block, not the memory block. When a bad memory cell is detected, not the whole accessed memory block but a part of the accessed memory block may be treated as a bad area. Accordingly, the number of unused memory cells is reduced by managing a bad area.

While some example embodiments have been particularly shown and described, it will be understood by one of ordinary skill in the art that variations in form and detail may be made therein without departing from the spirit and scope of the claims.

What is claimed is:

1. A bad area managing method comprising:

accessing one of a plurality of memory blocks on a substrate in a nonvolatile memory device, each one of the memory blocks containing memory layers stacked on top of each other on the substrate;

judging whether at least one memory layer of the memory layers in the accessed memory block includes a bad memory cell; and

if a bad memory cell is detected in the at least one memory layer, configuring the memory device to treat the at least one memory layer of the accessed memory block as a bad area.

2. The bad area managing method of claim 1, wherein the configuring the memory device to treat the at least one memory layer of the accessed memory block as a bad area comprises:

treating a lower one of the memory layers that is between the at least one memory layer containing the bad

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memory cell and the substrate, together with the at least one memory layer containing the bad memory cell, as a bad area.

3. The bad area managing method of claim 1, wherein the configuring the memory device to treat the at least one memory layer of the accessed memory block as a bad area comprises:

treating all memory layers between the at least one memory layer containing the bad memory cell and the substrate, together with the at least one memory layer containing the bad memory cell, as a bad area.

4. The bad area managing method of claim 1, wherein each memory layer includes a plurality of memory cells, each memory block includes a semiconductor pillar that penetrates the memory layers of the memory block, and the semiconductor pillar of each memory block defines channels of the plurality of memory cells contained within the memory block.

5. The bad area managing method of claim 4, wherein the configuring the memory device to treat the at least one memory layer of the accessed memory block as a bad area comprises treating another memory layer other than the at least one memory layer containing the bad memory cell, together with the at least one memory layer containing the bad memory cell, as a bad area; and wherein the semiconductor pillar includes a first width that is wider than a second width of the semiconductor pillar, the first width corresponding to the at least one memory layer containing the bad memory cell, and the second width corresponding to the another memory layer.

6. The bad area managing method of claim 1, wherein the plurality of memory layers in each memory block are divided into a plurality of sub memory blocks, and the configuring the memory device to treat the at least one memory layer of the accessed memory block as a bad area includes,

treating at least one sub-memory block of the accessed memory block as a bad area, the at least one sub-memory block containing the bad memory cell.

7. The bad area managing method of claim 6, wherein the configuring the memory device to treat the at least one memory layer of the accessed memory block as a bad area comprises treating another sub-memory block other than the sub-memory block containing the bad memory cell, together with the sub-memory block including the bad memory cell, as a bad area;

wherein each sub-memory block includes a semiconductor pillar that penetrates the memory layers of the sub-memory block; and

wherein the semiconductor pillar includes a first width that is wider than a second width of the semiconductor pillar, the first width corresponding to the sub-memory block containing the bad memory cell and the second width corresponding to the another sub-memory block.

8. The bad area managing method of claim 1, wherein each memory block includes a plurality of memory cells and a semiconductor pillar, the semiconductor pillar penetrating the memory layers of the memory block;

wherein the semiconductor pillar of each memory block defines channels of memory cells contained within the memory block;

wherein the semiconductor pillar includes first and second sub semiconductor pillars that are perpendicular to the

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substrate and the first sub semiconductor pillar penetrates the at least one memory layer including the bad memory cell;

wherein a first width of the first sub semiconductor pillar is wider than a second width of the first sub semiconductor pillar;

wherein the first width corresponds to the at least one sub-memory layer including the bad memory cell and the second width corresponds to the at least one sub-memory layer

wherein the configuring the memory device to treat the at least one memory layer of the accessed memory block as a bad area comprises,

treating another memory layer penetrated by the first sub semiconductor pillar, together with the at least one memory layer containing the bad memory cell, as a bad area.

9. The bad area managing method of claim 1, wherein, if a bad memory cell is detected in the at least one memory layer, the configuring the memory device further includes treating a portion of the accessed memory block as a normal area, and

the portion of the accessed memory block includes other ones of the memory layers in the accessed block that are separate from the at least one memory layer treated as a bad area.

10. A nonvolatile memory device comprising:

a nonvolatile memory portion including a plurality of memory blocks,

each of the plurality of memory blocks containing memory layers stacked on a substrate; and

a controller configured to manage at least one memory layer of an accessed one of the plurality of memory blocks as a bad area when the memory device detects a bad memory cell in the at least one memory layer of the accessed memory block.

11. The nonvolatile memory device of claim 10, wherein the controller comprises:

an address management register configured to store bad area information about the bad area; and

an address management circuit configured to update the bad area information such that the at least one memory layer including the bad memory cell is managed as the bad area.

12. The nonvolatile memory device of claim 11, wherein the address management circuit is configured to provide a physical address based upon the bad area information, the nonvolatile memory portion being accessed according to the physical address,

wherein, at a program or read operation, the address management circuit is configured to provide the physical address by a page unit when the memory block including the bad area is selected and by a memory block unit when another memory block not including the bad area is selected.

13. The nonvolatile memory device of claim 10, wherein memory layers included in each memory block are divided into a plurality of sub-memory blocks stacked on the substrate, and

wherein the controller comprises,

an address management register configured to store bad area information about the bad area; and

an address management circuit configured to update the bad area information such that the at least one sub-memory block including the bad memory cell is managed as the bad area.

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14. The nonvolatile memory device of claim 13,
 wherein the address management circuit is configured to
 provide a physical address based upon the bad area
 information,
 wherein the nonvolatile memory portion is configured to
 accessed according to the physical address, and
 wherein at a program or read operation, the address man-
 agement circuit is configured to provide the physical
 address of a sub-memory block unit when a memory
 block including the bad area is selected and the physical
 address of a memory block unit when a memory block
 not including the bad area is selected.

15. The nonvolatile memory device of claim 10,
 wherein the controller is configured to treat another
 memory layer other than a memory layer including the
 bad memory cell, together with the memory layer
 including the bad memory cell, as a bad area;
 wherein each memory layer includes a plurality of memory
 cells;
 wherein each memory block includes a semiconductor pil-
 lar that penetrates the memory layers of the memory
 block;
 wherein the semiconductor pillar of each memory block
 defines channels of the plurality of memory cells con-
 tained within the memory block;
 wherein the semiconductor pillar includes a first width that
 is wider than a second width of the semiconductor pillar;
 and
 wherein the first width corresponds to the at least memory
 layer including the bad memory cell and the second
 width corresponds to the another memory layer.

16. The nonvolatile memory device of claim 10, wherein
 the controller is configured to manage a portion of the
 accessed one of the plurality of memory blocks as a
 normal area when the memory device detects a bad
 memory cell in the at least one memory layer of the
 accessed memory block, and
 the portion of the accessed memory block includes other
 ones of the memory layers in the accessed block that are
 separate from the at least one memory layer of the
 accessed memory block that includes a bad memory cell.

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17. A nonvolatile memory device comprising:
 a nonvolatile memory portion including a plurality of
 memory blocks on a substrate,
 each memory block including a plurality of memory
 layers stacked on top of each other,
 each memory layer containing a plurality of cell transis-
 tors;
 a controller configured to manage at least one of the
 memory layers in a first part of one of the memory blocks
 as a bad area and to treat the memory layers in a second
 part of the one of the memory blocks as a normal area if
 the memory device detects a bad cell transistor in the
 first part of the one of the plurality of memory blocks and
 does not detect a bad cell transistor in the second part of
 the one of the plurality of memory blocks.

18. The nonvolatile memory device of claim 17, wherein
 the controller is configured to detect a bad cell transistor in
 the nonvolatile memory portion in response to receiving
 at least one of a read fail signal, a program fail signal, and
 an erase fail signal when at least one of the plurality of
 memory blocks is accessed by the controller.

19. The nonvolatile memory device of claim 17, wherein
 each memory block includes a plurality of sub-memory
 blocks,
 each sub-memory block contains at least two of the
 memory layers in the memory block, and
 the controller is configured to manage the at least one of the
 memory layers in the first part of the one of the memory
 blocks as a bad area during a first programming opera-
 tion by,
 storing data of the first programming operation in a
 first-sub memory block of a first memory block, and
 storing data of the first programming operation in at least
 one other memory block when the memory device
 detects the first memory block includes another sub-
 memory block containing a bad cell transistor and the
 other memory block does not contain a bad cell tran-
 sistor.

20. A computing system comprising:
 a CPU connected via a system bus to the nonvolatile
 memory device according of claim 17.

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